TAS5722L 15W 数字输入单声道 D 类音频放大器

1 特性

- 单声道 D 类放大器
  - 0.02% THD 时为 4Ω/17V 持续提供 15W 功率
- > 90% 的高效 D 类运行，省去了散热器
- 音频性能（PVDD = 16.5V，RSPK = 4Ω）
  - 空闲声道噪声 = 45μVRMS (A-Wtd)
  - 总谐波失真 + 噪声 (THD+N) = 0.04% (1W/1kHz)
  - 信噪比 (SNR) = 106dB A-Wtd（参考 THD+N = 1%）
- I^2S 输入：32kHz 至 96kHz
- 时分复用 (TDM) 音频输入
  - 多达 8 条声道（32 位，96kHz）
- I^2C 控制，通过 8 个可选 I^2C 地址实现
- 电源
  - 功率放大器：4.5V 至 17V
  - 数字 I/O 电压：1.8V
- 稳定性 特性
  - 时钟误差检测器、直流偏移和短路保护
  - 过压、欠压和过热保护

2 应用

- 低音炮、音箱、条形音响、楼宇自动化
- 有源扬声器，个人计算机
- 环绕立体声系统，单声道音频系统

3 说明

TAS5722L器件是一款高效单声道 D 类音频功率放大器，其中包含集成的数字输出削波器、多个增益选项和广泛的电源电压范围。该器件的标称电源电压范围为 4.5V 至 17 VDC。

TAS5722L 已针对高瞬态功率能力进行优化，能够利用小型扬声器的动态功率余量。可持续为 4Ω 的扬声器提供超过 15W 的功率。

数字时分复用 (TDM) 接口支持多达 8 个器件共用同一条总线。

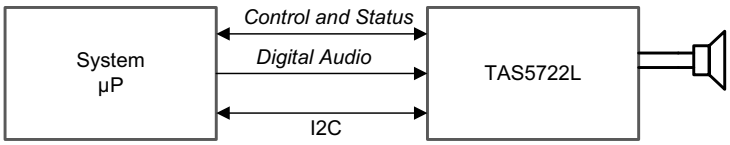
TAS5722L器件采用 4mm x 4mm 32 引脚四方扁平无引线 (QFN) 封装。

器件信息(1)

器件名称	封装	封装尺寸
TAS5722L	QFN (32)	4mm x 4mm

(1) 要了解所有可用封装，请见文档末尾的可订购产品附录。

简化电路原理图



Copyright © 2016, Texas Instruments Incorporated

目录

1 特性 1
2 应用 1
3 说明 1
4 修订历史记录 2
5 **Pin Configuration and Functions** 3
6 **Specifications** 5
6.1 Absolute Maximum Ratings 5
6.2 ESD Ratings 5
6.3 Recommended Operating Conditions 5
6.4 Thermal Information 6
6.5 Electrical Characteristics 7
6.6 Timing Requirements 9
6.7 Typical Characteristics 12
7 **Detailed Description** 17
7.1 Overview 17
7.2 Functional Block Diagram 17
7.3 Feature Description 17
7.4 Device Functional Modes 29
7.5 Register Maps 31
8 **Applications and Implementation** 39
8.1 Application Information 39
8.2 Typical Application 39
9 **Power Supply Recommendations** 41
10 **Layout** 41
10.1 Layout Guidelines 41
10.2 Layout Example 42
11 器件和文档支持 43
11.1 商标 43
11.2 静电放电警告 43
11.3 Glossary 43
12 机械封装和可订购信息 44
12.1 Package Option Addendum 45

4 修订历史记录

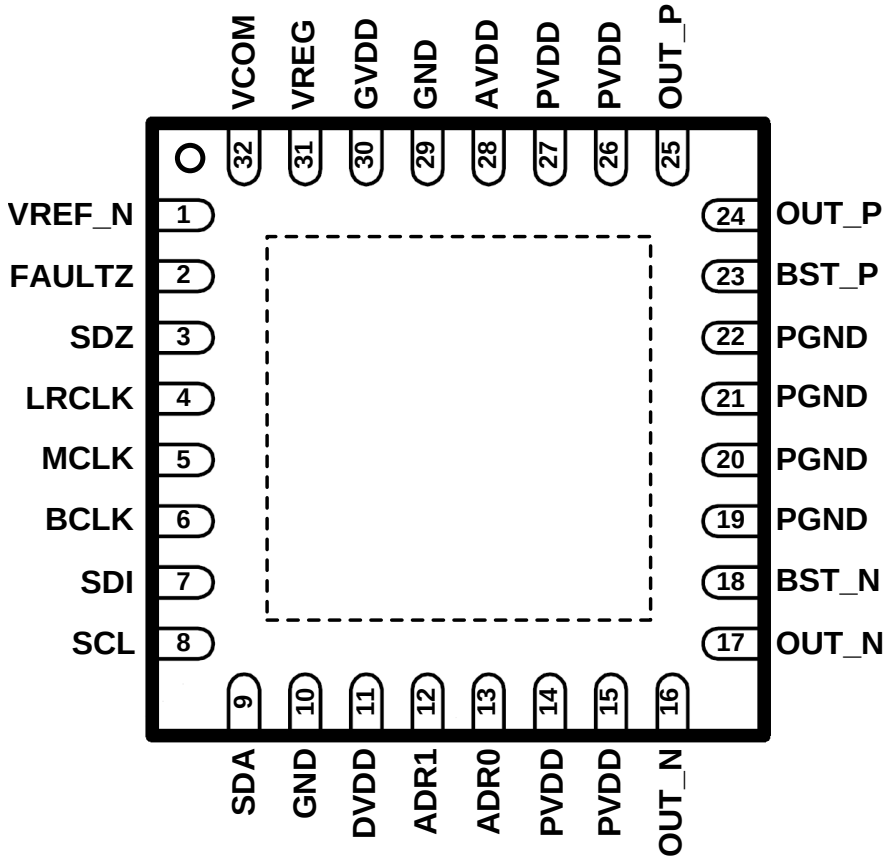
注：之前版本的页码可能与当前版本有所不同。

Changes from Original (May 2016) to Revision A	Page
• 已将产品更改为量产数据。	1

Copyright © 2016, Texas Instruments Incorporated

5 Pin Configuration and Functions

RSM PACKAGE
32 PINS
(TOP VIEW)



Pin Functions[1]

PIN		I/O/P[2]	DESCRIPTION
NAME	NO.		
ADR1	12	I	I^2C address inputs. Each pin can detect a short to DVDD, a short to GND, a 22-kΩ connection to GND and a 22-kΩ connection to DVDD.
ADR0	13	I	
AVDD	28	P	Analog power supply input. Connect directly to PVDD.
BCLK	6	I	TDM Interface serial bit clock.
BST_N	18	P	Class-D Amplifier negative bootstrap. Connect a capacitor between BST_N and OUT_N.
BST_P	23	P	Class-D Amplifier positive bootstrap. Connect a capacitor between BST_P and OUT_P.
DVDD	11	P	Digital power supply. Connect to 1.8-V supply with external decoupling capacitor.
FAULTZ	2	O	Open drain active low fault flag. Pull up on PCB with resistor to DVDD.
GND	10 29	P	Ground. Connect to PCB ground plane.
GVDD	30	O	Class-D amplifier gate drive regulator output. Connect decoupling cap to PCB ground plane.
LRCLK	4	I	TDM interface left/right clock.
MCLK	5	I	Device master clock.

(1) Connect exposed thermal pad to PCB ground plane
(2) I = input, O = output, P = power, I/O = bi-directional

Copyright © 2016, Texas Instruments Incorporated

Pin Functions[1] (continued)

PIN		I/O/P[2]	DESCRIPTION
NAME	NO.		
PGND	19 20 21 22	P	Power ground. Connect to PCB ground plane.
PVDD	14 15 26 27	P	Class-D amplifier power supply input. Connect to PVDD supply and decouple externally.
OUT_N	16 17	O	Class-D amplifier negative output.
OUT_P	24 25	O	Class-D amplifier positive output.
SCL	8	I	I^2C clock Input. Pull up on PCB with a 2.4-kΩ resistor.
SDA	9	I/O	I^2C bi-directional data. Pull up on PCB with a 2.4-kΩ resistor.
SDI	7	I	TDM interface data input.
SDZ	3	I	Active low shutdown signal. Assert low to hold device inactive.
VCOM	32	O	Common mode reference output. Connect decoupling capacitor to the VREF_N pin.
VREF_N	1	P	Negative reference for analog. Connect to VCOM and VREG capacitor negative pins.
VREG	31	O	Analog regulator output. Connect decoupling capacitor to the VREF_N pin.

Copyright © 2016, Texas Instruments Incorporated

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)	PVDD, AVDD	–0.3	20	V
		DVDD	–0.3	2.25	
	Digital input voltage	Digital inputs referenced to DVDD supply	–0.5	V_{DVDD} + 0.5	V
T_A	Ambient operating temperature		–25	85	°C
T_{stg}	Storage temperature range		–40	125	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods my affect device reliability.
(2) All voltages are with respect to network ground pin.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP	MAX	UNIT
PVDD AVDD	Power supply voltage	4.5		17	V
DVDD	Power supply voltage	1.65	1.8	2	V
$V_{IH(DR)}$	High-level digital input voltage		V_{DVDD}		V
$V_{IL(DR)}$	Low-level digital input voltage		0		V
R_{SPK}	Minimum speaker load	3.2			Ω
T_A	Operating free-air temperature	–25		85	°C
T_J	Operating junction temperature	–25		150	°C

版权 © 2016, Texas Instruments Incorporated

6.4 Thermal Information

THERMAL METRIC(1)		TAS5722L RSM (QFN) 32 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance(2)	37.3	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance(3)	30.4	
$R_{\theta JB}$	Junction-to-board thermal resistance(4)	7.9	
ψ_{JT}	Junction-to-top characterization parameter(5)	0.4	
ψ_{JB}	Junction-to-board characterization parameter(6)	7.7	
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance(7)	2.5	

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report (SPRA953).
(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
(5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining $R_{\theta JA}$, using a procedure described in JESD51-2a (sections 6 and 7).
(6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining $R_{\theta JA}$, using a procedure described in JESD51-2a (sections 6 and 7).
(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

版权 © 2016, Texas Instruments Incorporated

6.5 Electrical Characteristics

V_{PVDD} = 16.5 V, V_{DVDD} = 1.8 V, R_L = 4 Ω + 33 µH, f_{PWM} = 576 kHz, 22-Hz to 20- kHz Bandwidth, AP AUX-0025 + AES17 Filter (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
DIGITAL INPUT AND OUTPUT						
V_{IH}	High-level digital input logic voltage threshold	All digital pins	70%			
V_{IL}	Low-level digital input logic voltage threshold	All digital pins			30%	
I_{IH}	Input logic "high" leakage for digital inputs	All digital pins, excluding SDZ			15	µA
I_{IL}	Input logic "low" leakage for digital inputs	All digital pins, excluding SDZ			–15	µA
$I_{IH(SDZ)}$	Input logic "high" leakage for SDZ inputs	SDZ			1	µA
$I_{IL(SDZ)}$	Input logic "low" leakage for SDZ inputs	SDZ			–1	µA
V_{OL}	Output logic "low" for FAULTZ open drain Output	I_{OL} = –2 mA			10% V_{DVDD}	
C_{IN}	Input capacitance for digital inputs	All digital pins		5		pF
MASTER CLOCK						
D_{MCLK}	Allowable MCLK duty cycle		45%	50%	55%	
f_{MCLK}	MCLK input frequency				25	MHz
	Supported single-speed MCLK frequencies	values: 64, 128, 256 and 512	2.8		24.6	MHz
	Supported double-speed MCLK frequencies	values: 64, 128 and 256	5.6		24.6	MHz
SERIAL AUDIO PORT						
D_{BCLK}	Allowable BCLK duty cycle		45%	50%	55%	
f_{BCLK}	BCLK input frequency				25	MHz
	Supported single-speed BCLK frequencies	values: 64, 96, 128, 192 and 256	2.8		12.3	MHz
	Supported double-speed BCLK frequencies	values: 64, 96, 128, 192 and 256	5.6		24.6	MHz
f_S	Supported single-speed input sample rates	values: 44.1 and 48	44.1		48	kHz
	Supported double-speed input sample rates	values: 88.2 and 96	88.2		96	kHz
I^2C CONTROL PORT						
$C_{L(I2C)}$	Allowable load capacitance for each I^2C Line				400	pF
f_{SCL}	SCL frequency	No wait states			400	kHz
PROTECTION						
OTE_{THRESH}	Over-temperature error (OTE) threshold			150		°C
OTE_{HYST}	Over-temperature error (OTE) hysteresis			15		°C
OCE_{THRESH}	overcurrent error (OCE) threshold	V_{PVDD} = 16.5 V, T_A = 25°C		5		A
DCE_{THRESH}	DC error (DCE) threshold	V_{PVDD} = 16.5V, TA = 25°C		2.6		V

版权 © 2016, Texas Instruments Incorporated

Electrical Characteristics (接下页)

V_{PVDD} = 16.5 V, V_{DVDD} = 1.8 V, R_L = 4 Ω + 33 µH, f_{PWM} = 576 kHz, 22-Hz to 20- kHz Bandwidth, AP AUX-0025 + AES17 Filter (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
AMPLIFIER PERFORMANCE						
P_{OUT}	Continuous average power	R_L = 8 Ω+33 µH, 1% THD+N, V_{PVDD} = 12 V, f_{IN} = 1 kHz		8.2		W
		R_L = 8 Ω+33 µH, 1% THD+N, V_{PVDD} = 16.5 V, f_{IN} = 1 kHz		15.25		
		R_L = 4 Ω+33 µH, 1% THD+N, V_{PVDD} = 12 V, f_{IN} = 1 kHz		14.25		
		R_L = 4 Ω+33 µH, 1% THD+N, V_{PVDD} = 16.5 V, f_{IN} = 1 kHz		16		
THD+N	Total harmonic distortion plus noise	R_L = 8 Ω+33 µH, V_{PVDD} = 12 V, P_{OUT} = 4.25 W, 20 Hz ≤ f_{IN}≤ 20 kHz		0.05%		
		R_L = 8 Ω+33 µH, V_{PVDD} = 16.5 V, P_{OUT} = 4.25 W, 20 Hz ≤ f_{IN}≤ 20 kHz		0.05%		
		R_L = 4 Ω+33 µH, V_{PVDD} = 12 V, P_{OUT} = 8.25 W, 20 Hz ≤ f_{IN}≤ 20 kHz		0.05%		
		R_L = 4 Ω+33 µH, V_{PVDD} = 16.5 V, P_{OUT} = 8.25 W, 20 Hz ≤ f_{IN}≤ 20 kHz		0.06%		
P_{EFF}	Power efficiency	R_L = 8 Ω+33 µH, V_{PVDD} = 16.5 V, P_{OUT} = 10 W		90%		
		R_L = 4 Ω+33 µH, V_{PVDD} = 16.5 V, P_{OUT} = 14 W		87%		
V_N	Integrated noise floor voltage	A-Weighted, Gain = 20.7dBV, R_L = 8 Ω+33 µH		50		µVrms
KCP	Click-pop performance	Into and out of HW reset, into and out of SW shutdown, when SAIF clocks are applied or removed and during power rail cycling. Measured using Maxim click-pop measurement method.		-60		dB
φ_{CC}	Channel-to-channel phase shift	Output phase shift between multiple devices from 20 Hz to 20 kHz. Across all sample frequencies and SAIF operating modes.		0.2		deg
PSRR	Power supply rejection ratio	AC, 5.5 V ≤ V_{PVDD} ≤ 16.5 V, DVDD = 1.8 V+200 mV_{P-P}, f_{RIPPLE} from 20 Hz to 20 kHz		69		dB
		AC, V_{PVDD} = 16.5 V+200 mV_{P-P}, f_{RIPPLE} from 20 Hz to 5 kHz		64		
		AC, V_{PVDD} = 16.5 V+100 mV_{P-P}, f_{RIPPLE} from 5 kHz to 20 kHz		60		
AV_{00}	Amplifier analog gain (1)	ANALOG_GAIN[1:0] register bits set to "00"		19.2		dBV
AV_{01}		ANALOG_GAIN[1:0] register bits set to "01"		20.7		dBV
AV_{10}		ANALOG_GAIN[1:0] register bits set to "10"		23.5		dBV
AV_{11}		ANALOG_GAIN[1:0] register bits set to "11"		26.3		dBV
AV_{ERROR}	Amplifier analog gain error				±0.15	dB
V_{OS}	DC output offset voltage	Measured between OUTP and OUTN		1.5		mV
A_{RIPPLE}	Frequency response	Maximum deviation above or below passband gain.		±0.15		dB
f_{LP}	-3 dB Output Cutoff Frequency			0.47×f_S		Hz
$R_{DS(on)FET}$	Power stage FET on-resistance	T_A = 25°C		120		mΩ

(1) When PVDD is less than 5.5 V, the voltage regulator that operates the analog circuitry does not have enough headroom to maintain the nominal 5.4-V internal voltage. The lack of headroom causes a direct reduction in gain (approximately –0.8 dB at 5 V and –1.74 dB at 4.5 V), but the device functions properly down to V_{PVDD} = 4.5 V. For operation below 5.5V, the VREG_LVL bit (register 0x14, bit 2) can be set high, which reduces the internal voltage regulator output voltage to prevent variation in gain. When the bit is set high, all gain settings are reduced by 3dB.

版权 © 2016, Texas Instruments Incorporated

Electrical Characteristics (接下页)

V_{PVDD} = 16.5 V, V_{DVDD} = 1.8 V, R_L = 4 Ω + 33 µH, f_{PWM} = 576 kHz, 22-Hz to 20- kHz Bandwidth, AP AUX-0025 + AES17 Filter (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
$R_{DS(on)TOT}$	Power stage total on-resistance (FET+bond+package)	T_A = 25°C		150		mΩ
I_{P-P}	Peak output current	T_A = 25°C		5		A
f_{PWM}	PWM switching frequency	values: 6, 8, 10, 12, 14, 16, 20 and 24	6		24	MHz

6.6 Timing Requirements

			MIN	NOM	MAX	UNIT
t_{ACTIVE}	Shutdown to Active Time	From deassertion of SDZ (both pin and I^2C register bit) until the Class-D amplifier begins switching.		25		ms
t_{WAKE}	Wake Time	From the deassertion of SLEEP until the Class-D amplifier starts switching.		1		ms
t_{SLEEP}	Sleep Time	From the assertion of SLEEP until the Class-D amplifier stops switching.		t_{vrmp}+1		ms
t_{MUTE}	Play to Mute Time	From the assertion of MUTE until the volume has ramped to the minimum.		t_{vrmp}		ms
t_{PLAY}	Un-Mute to Play Time	From the deassertion of MUTE until the volume has returned to its current setting.		t_{vrmp}		ms
t_{SD}	Active to Shutdown Time	From the assertion of SDZ (pin or I^2C register bit) until the Class-D amplifier stops switching.		t_{vrmp}+1		ms

版权 © 2016, Texas Instruments Incorporated

Timing Requirements (接下页)

			MIN	NOM	MAX	UNIT
SERIAL AUDIO PORT						
t_{H_L}	Time High/Low, BCLK, LRCLK, SDI inputs		10			ns
t_{SU} / t_{HLD}	Setup and hold time. LRCLK, SDI input to BCLK edge.	Input t_{RISE} ≤ 1 ns, input t_{FALL} ≤ 1 ns	5			ns
		Input t_{RISE} ≤ 4 ns, input t_{FALL} ≤ 4ns	8			
		Input t_{RISE} ≤ 8 ns, input t_{FALL} ≤ 8ns	12			
t_{RISE}	Rise-time BCLK, LRCLK, SDI inputs				8	ns
t_{FALL}	Fall-time BCLK, LRCLK, SDI inputs				8	ns
I²C CONTROL PORT						
t_{BUF}	Bus free time between start and stop conditions		1.3			µs
$t_{H1(I2C)}$	Hold Time, SCL to SDA		0			ns
$t_{H2(I2C)}$	Hold Time, start condition to SCL		0.6			µs
$t_{START(I2C)}$	I2C Startup Time after DVDD Power On Reset				12	ms
$t_{R(I2C)}$	Rise Time, SCL and SDA				300	ns
$t_{F(I2C)}$	Fall Time, SCL and SDA				300	ns
$t_{SU1(I2C)}$	Setup, SDA to SCL		100			ns
$t_{SU2(I2C)}$	Setup, SCL to start condition		0.6			µs
$t_{SU3(I2C)}$	Setup, SCL to stop condition		0.6			µs
$t_{W(H)}$	Required pulse duration, SCL "HIGH"		0.6			µs
$t_{W(L)}$	Required pulse duration, SCL "LOW"		1.3			µs
PROTECTION						
t_{FAULTZ}	Amplifier fault time-out period	DC detect error		650		ms
		OTE or OCE fault		1.3		s

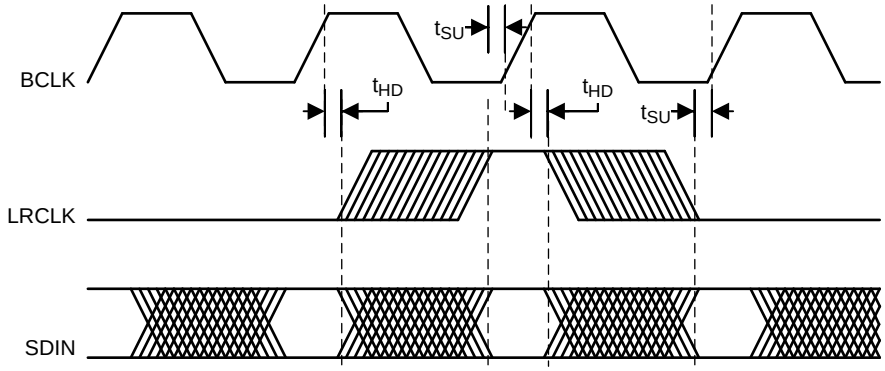


图 1. SAIF Timing

版权 © 2016, Texas Instruments Incorporated

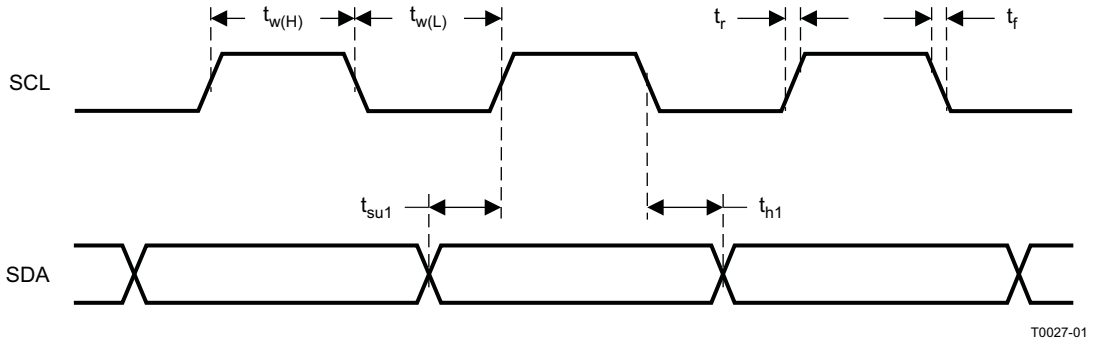


图 2. SCL and SDA Timing

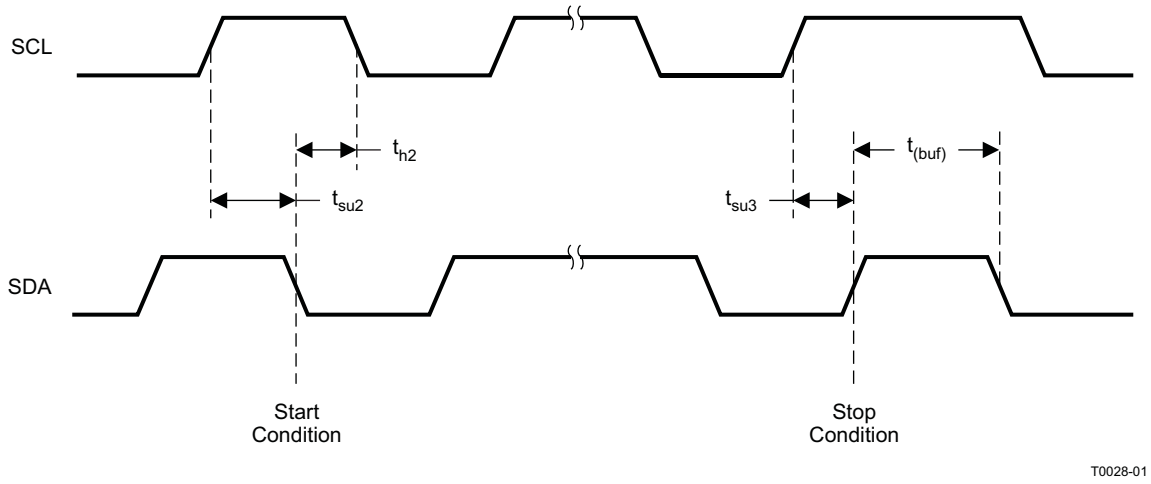


图 3. Start and Stop Conditions Timing

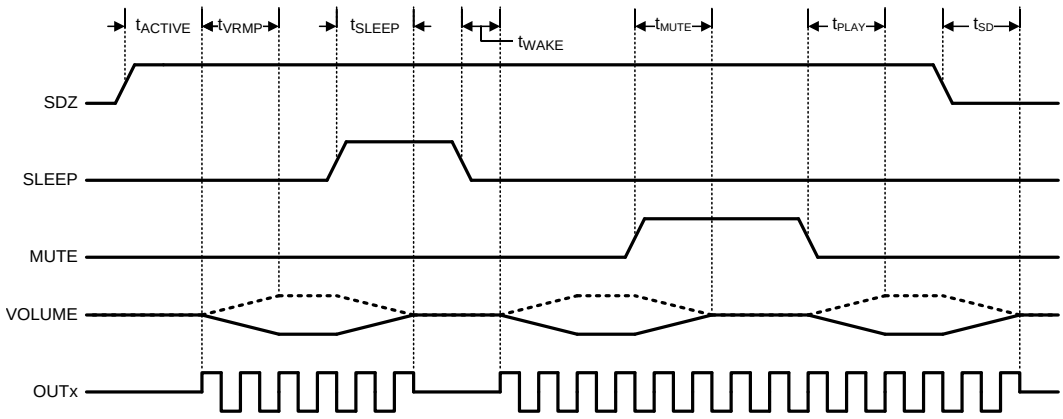


图 4. Mode Timing

6.7 Typical Characteristics

T_A = 25ºC, V_{DVDD} = 1.8 V, f_{IN} = 1 kHz, f_{PWM} 768 kHz, f_s = 48 kHz, Gain = 20.7 dBV, SDZ = 1, Measured using TAS5722LEVM with an Audio Precision SYS-2722 and AUX-0025 filter with 22-Hz-to-20- kHz un-weighted bandwidth using the 20- kHz pre-analyzer filter + 20- kHz brick-wall filter (unless otherwise specified). 33 µH inductors were added in series with 4 Ω loads and 68 µH inductors were placed in series with 8 Ω loads due to the ferrite bead filters.

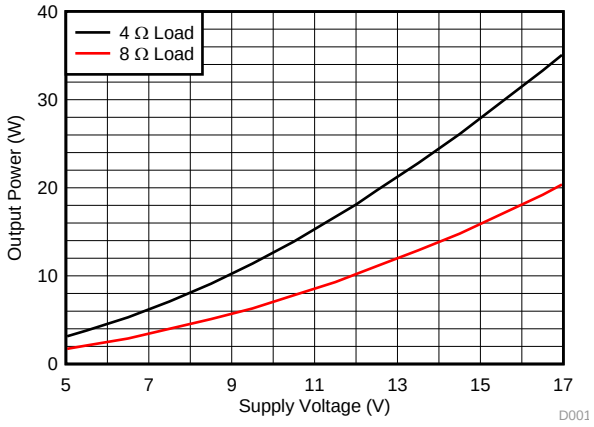
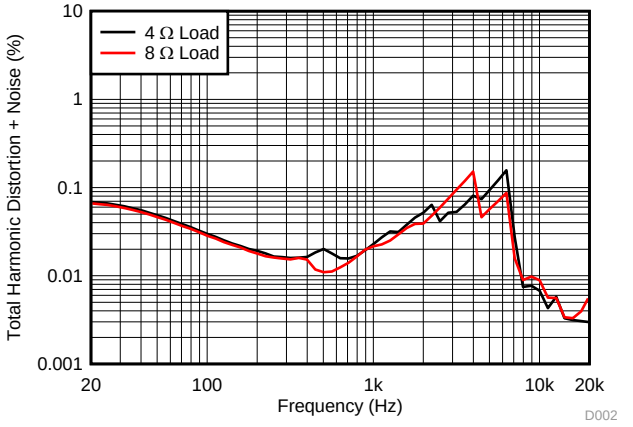
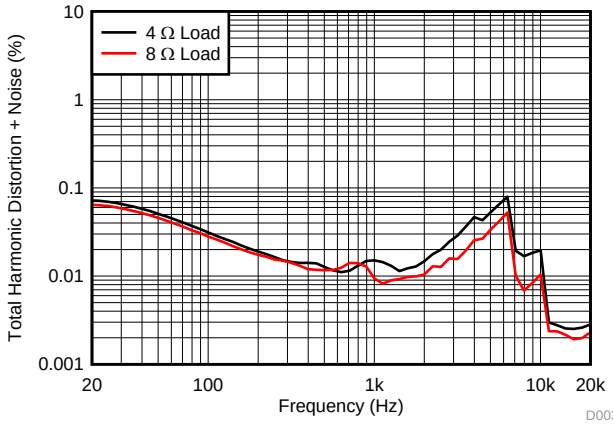


图 5. Output Power vs Supply Voltage



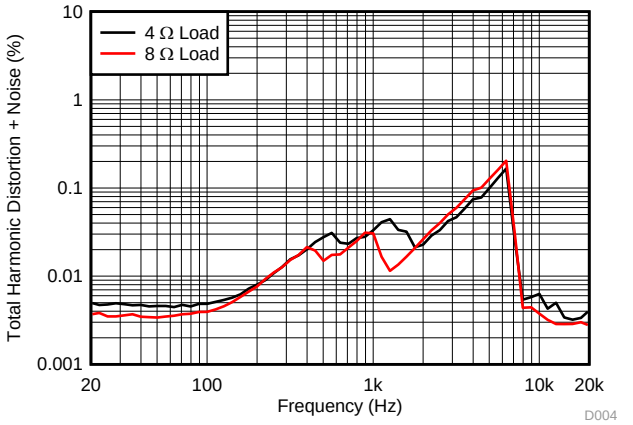
PV_{DD} = 5 V Gain = 19.2 dBV f_{PWM} = 384 kHz

图 6. THD+N vs Frequency



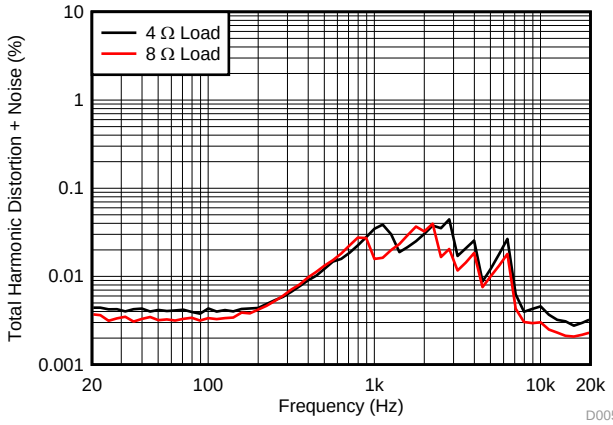
PV_{DD} = 5 V Gain = 19.2 dBV f_{PWM} = 768 kHz

图 7. THD+N vs Frequency



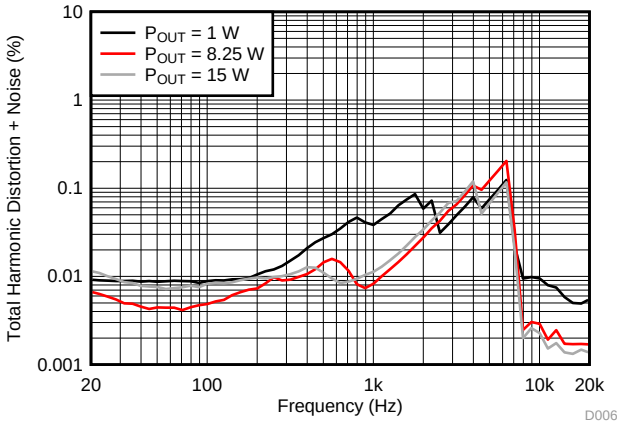
PV_{DD} = 12 V Gain = 19.2 dBV f_{PWM}= 384 kHz

图 8. THD+N vs Frequency



PV_{DD} = 12 V Gain = 19.2 dBV f_{PWM} = 768 kHz

图 9. THD+N vs Frequency



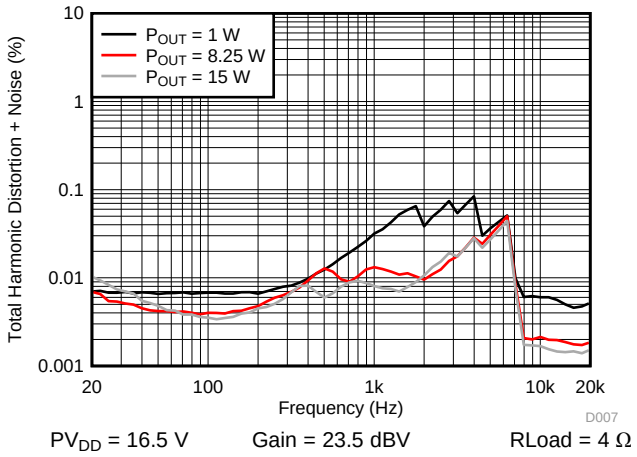
PV_{DD} = 16.5 V Gain = 23.5 dBV f_{PWM} = 384 kHz
RLoad = 4 Ω

图 10. THD+N vs Frequency

版权 © 2016, Texas Instruments Incorporated

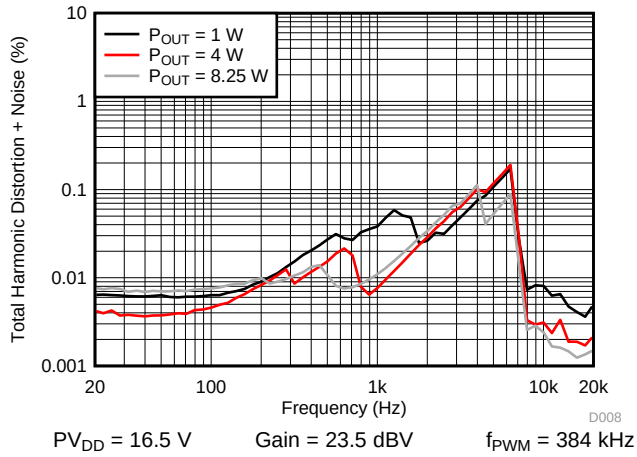
Typical Characteristics (接下页)

T_A = 25ºC, V_{DVDD} = 1.8 V, f_{IN} = 1 kHz, f_{PWM} 768 kHz, f_s = 48 kHz, Gain = 20.7 dBV, SDZ = 1, Measured using TAS5722LEVM with an Audio Precision SYS-2722 and AUX-0025 filter with 22-Hz-to-20- kHz un-weighted bandwidth using the 20- kHz pre-analyzer filter + 20- kHz brick-wall filter (unless otherwise specified). 33 µH inductors were added in series with 4 Ω loads and 68 µH inductors were placed in series with 8 Ω loads due to the ferrite bead filters.



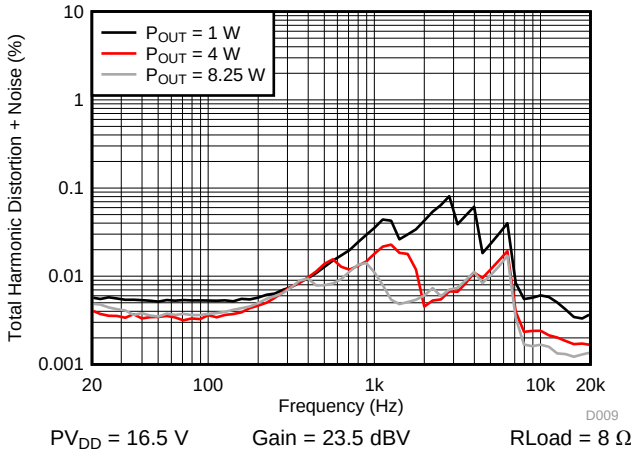
PV_{DD} = 16.5 V Gain = 23.5 dBV RLoad = 4 Ω

图 11. THD+N vs Frequency



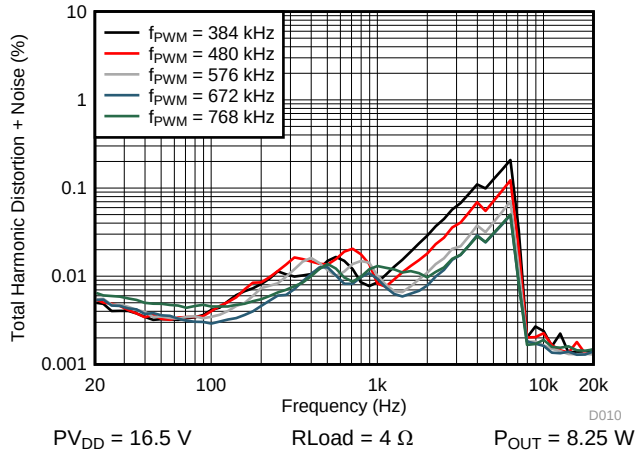
PV_{DD} = 16.5 V Gain = 23.5 dBV f_{PWM} = 384 kHz
RLoad = 8 Ω

图 12. THD+N vs Frequency



PV_{DD} = 16.5 V Gain = 23.5 dBV RLoad = 8 Ω

图 13. THD+N vs Frequency

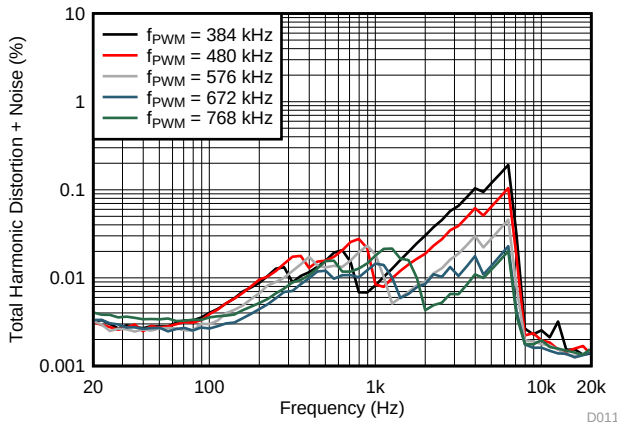


PV_{DD} = 16.5 V RLoad = 4 Ω P_{OUT} = 8.25 W

图 14. THD+N vs Frequency

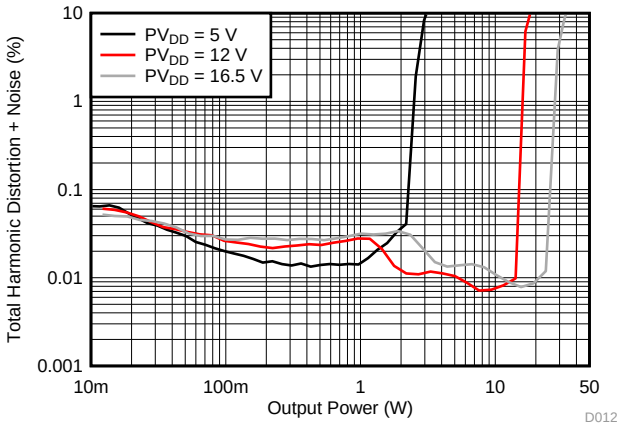
Typical Characteristics (接下页)

T_A = 25ºC, V_{DVDD} = 1.8 V, f_{IN} = 1 kHz, f_{PWM} 768 kHz, f_s = 48 kHz, Gain = 20.7 dBV, SDZ = 1, Measured using TAS5722LEVM with an Audio Precision SYS-2722 and AUX-0025 filter with 22-Hz-to-20- kHz un-weighted bandwidth using the 20- kHz pre-analyzer filter + 20- kHz brick-wall filter (unless otherwise specified). 33 µH inductors were added in series with 4 Ω loads and 68 µH inductors were placed in series with 8 Ω loads due to the ferrite bead filters.



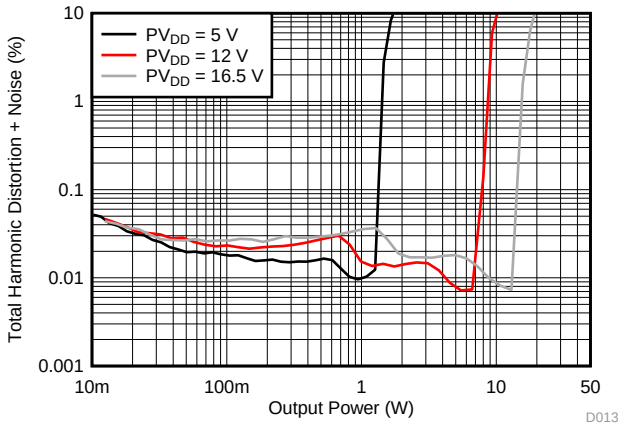
PV_{DD} = 16.5 V Gain = 20.7 dBV P_{OUT} = 4.25 W
RLoad = 8 Ω

图 15. THD+N vs Frequency



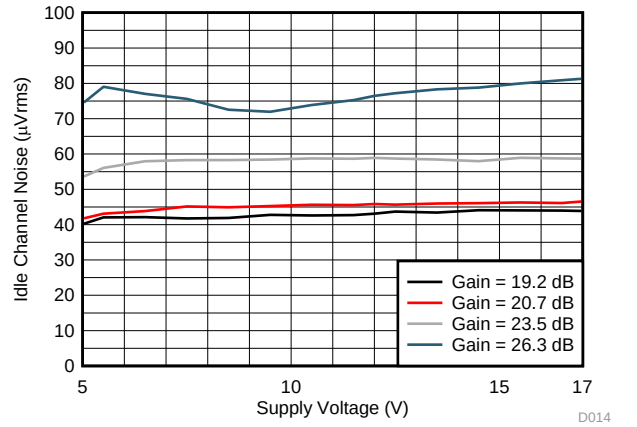
RLoad = 4 Ω Gain = 23.5 dBV f_{PWM} = 768 kHz

图 16. THD+N vs Output Power



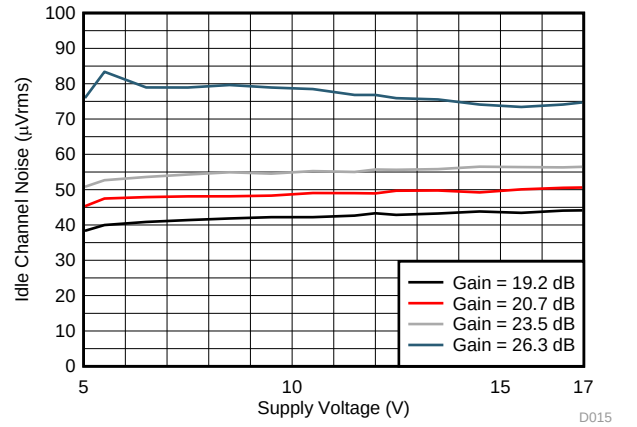
RLoad = 8 Ω Gain = 23.5 dBV f_{PWM} = 768 kHz

图 17. Idle Channel Noise vs Supply Voltage



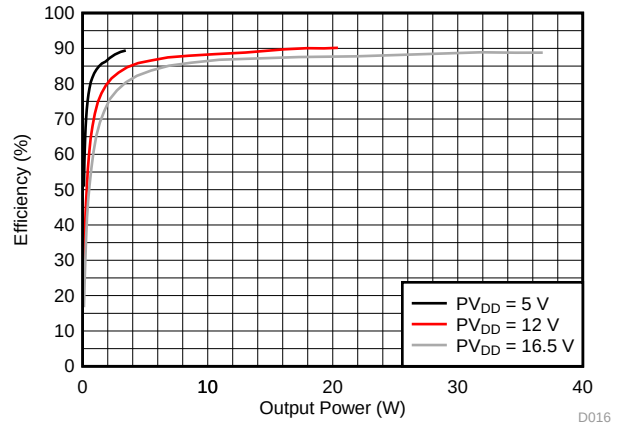
RLoad = 4 Ω A-weighting Filter f_{PWM} = 384 kHz

图 18. Idle Channel Noise vs Supply Voltage



RLoad = 4 Ω A-weighting Filter f_{PWM} = 768 kHz

图 19. Efficiency vs Output Power



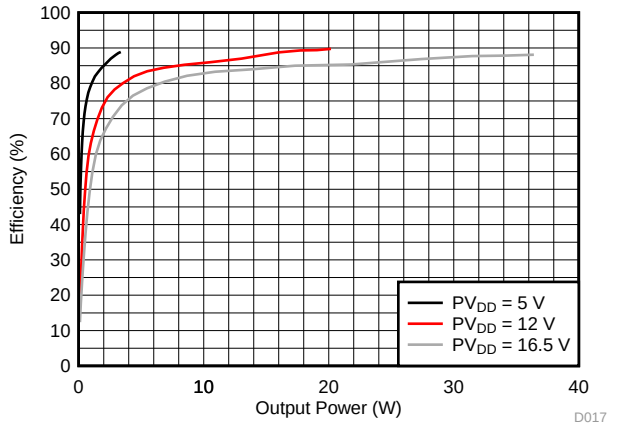
RLoad = 4 Ω Gain = 23.5 dBV f_{PWM} = 384 kHz

图 20. Efficiency vs Output Power

版权 © 2016, Texas Instruments Incorporated

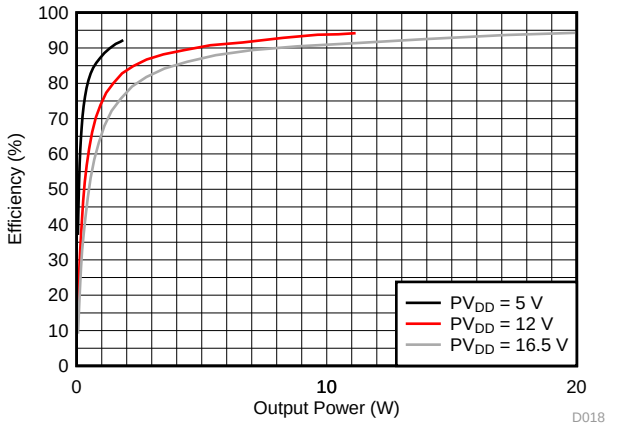
Typical Characteristics (接下页)

T_A = 25ºC, V_{DVDD} = 1.8 V, f_{IN} = 1 kHz, f_{PWM} 768 kHz, f_s = 48 kHz, Gain = 20.7 dBV, SDZ = 1, Measured using TAS5722LEVM with an Audio Precision SYS-2722 and AUX-0025 filter with 22-Hz-to-20- kHz un-weighted bandwidth using the 20- kHz pre-analyzer filter + 20- kHz brick-wall filter (unless otherwise specified). 33 µH inductors were added in series with 4 Ω loads and 68 µH inductors were placed in series with 8 Ω loads due to the ferrite bead filters.



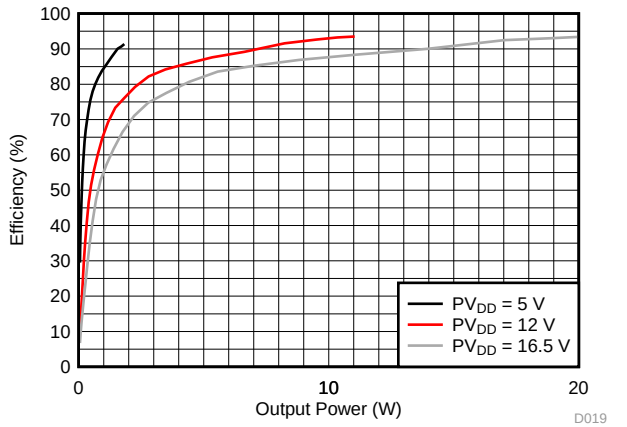
RLoad = 4 Ω Gain = 23.5 dBV f_{PWM} = 768 kHz

图 21. Efficiency vs Output Power



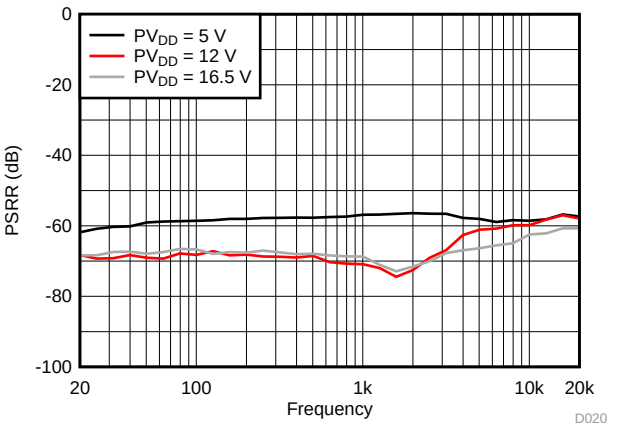
RLoad = 8 Ω Gain = 23.5 dBV f_{PWM} = 384 kHz

图 22. Efficiency vs Output Power



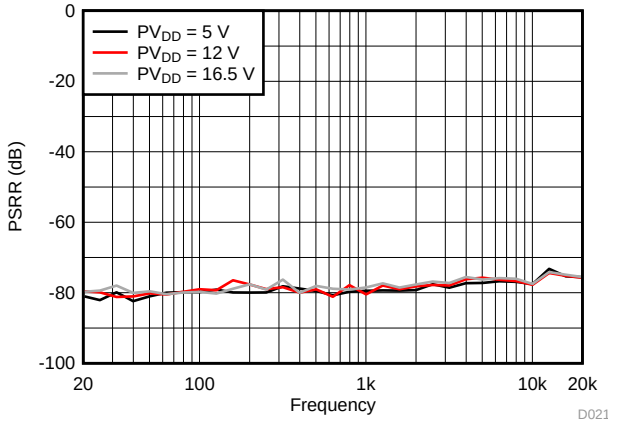
RLoad = 8 Ω Gain = 23.5 dBV f_{PWM} = 768 kHz

图 23. PV<Subscript>DD</Subscript> PSRR vs Frequency



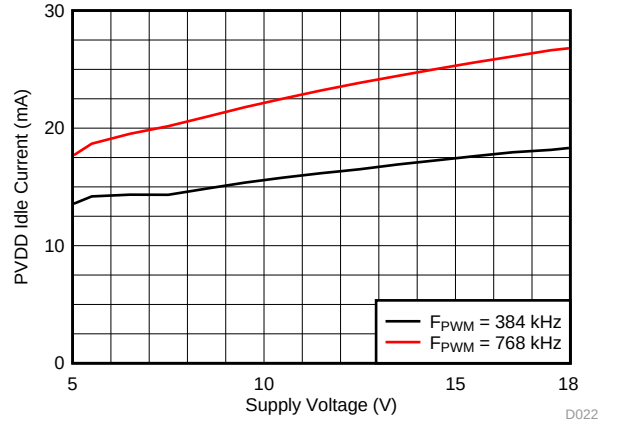
RLoad = 4 Ω Gain = 20.7 dBV f_{PWM} = 768 kHz

图 24. DVDD PSRR vs Frequency



RLoad = 4 Ω Gain = 20.7 dBV f_{PWM} = 768 kHz

图 25. Idle Current vs Supply Voltage



RLoad = 4 Ω Gain = 20.7 dBV

图 26. Shutdown Current vs Supply Voltage

Typical Characteristics (接下页)

T_A = 25ºC, V_{DVDD} = 1.8 V, f_{IN} = 1 kHz, f_{PWM} 768 kHz, f_s = 48 kHz, Gain = 20.7 dBV, SDZ = 1, Measured using TAS5722LEVM with an Audio Precision SYS-2722 and AUX-0025 filter with 22-Hz-to-20- kHz un-weighted bandwidth using the 20- kHz pre-analyzer filter + 20- kHz brick-wall filter (unless otherwise specified). 33 µH inductors were added in series with 4 Ω loads and 68 µH inductors were placed in series with 8 Ω loads due to the ferrite bead filters.

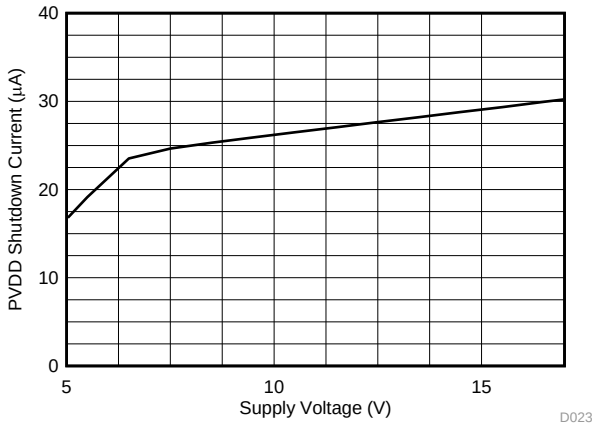


图 27. PVDD Shutdown Current vs Supply Voltage

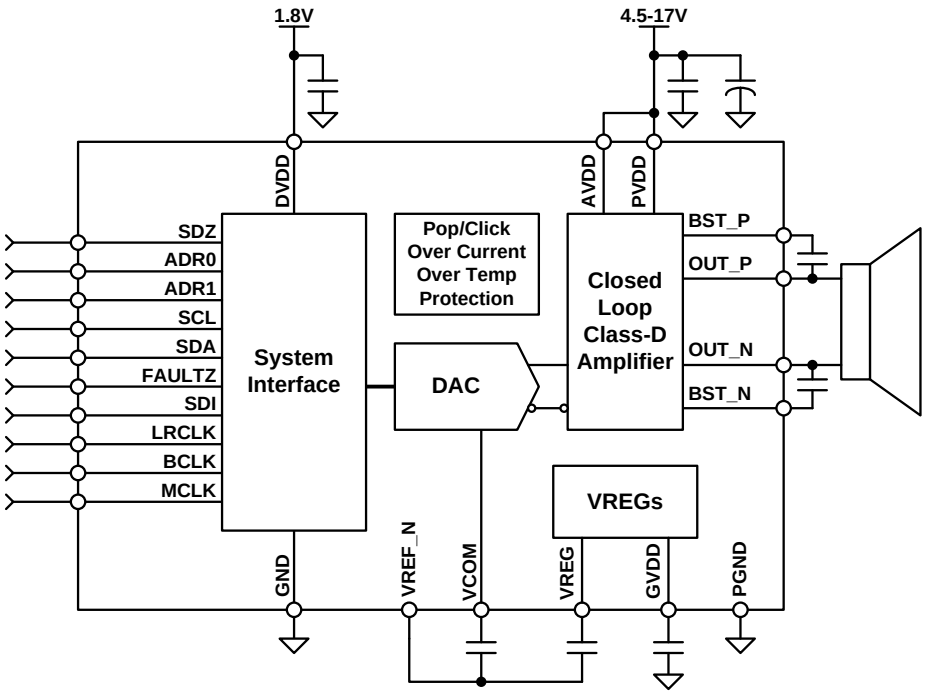
版权 © 2016, Texas Instruments Incorporated

7 Detailed Description

7.1 Overview

The TAS5722L device is a high-efficiency mono Class-D audio power amplifier optimized for high-transient power capability to utilize the dynamic power headroom of small loudspeakers. The TAS5722L device is capable of delivering more than 14 W continuously into a 4-Ω speaker.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Adjustable I²C Address

The TAS5722L device has two address pins, which allow up to 8 I²C addressable devices to share a common TDM bus. 表 1 lists each I²C *Device ID* setting.

注

The I²C Device ID is the 7 most significant bits of the 8-bit address transaction on the bus (with the read/write bit being the least significant bit). For example, a Device ID of 0x6C would be read as 0xD8 when the read/write bit is 0.

表 1. I²C Device Identifier (ID) Generation

ADR1	ADR0	I2C_DEV_ID	DEFAULT TDM SLOT
Short to GND	Short to GND	0x6C	0
	22-kΩ to GND	0x6D	1
	22-kΩ to DVDD	0x6E	2
	Short to DVDD	0x6F	3

表 1. I²C Device Identifier (ID) Generation (接下页)

ADR1	ADR0	I2C_DEV_ID	DEFAULT TDM SLOT
22-kΩ to GND	Short to GND	0x70	4
	22-kΩ to GND	0x71	5
	22-kΩ to DVDD	0x72	6
	Short to DVDD	0x73	7

Use a 22-kΩ resistor with a 5% (or better) tolerance as a pull-up or pull-down resistor. By default, the device uses the TDM time slot equal to its offset from the base I²C Device ID (see 表 1). The TDM slot can also be manually configured by setting the TDM_CFG_SRC bit high (bit 6, reg 0x02) and programming the TDM_SLOT_SELECT[3:0] bits to the desired slot (bits 0-3, reg 0x03).

For 2-channel, I²S operation, TDM slot 0 and 1 correspond to the right and left channels respectively. For left and right justified formats, TDM slot 0 and 1 correspond to left and right channels respectively.

7.3.2 I²C Interface

The TAS5722L device has a bidirectional I²C interface that is compatible with the Inter-Integrated Circuit (I²C) bus protocol and supports both 100 kHz and 400 kHz data transfer rates. The slave-only device does not support a multi-master bus environment or wait-state insertion. The control interface is used to program the registers of the device and to read device status.

The I²C bus employs two signals, SDA (data) and SCL (clock), to communicate between integrated circuits in a system. Data is transferred on the bus serially, one bit at a time. The address and data can be transferred in byte (8-bit) format, with the most-significant bit (MSB) transferred first. In addition, each byte transferred on the bus is acknowledged by the receiving device with an acknowledge bit. Each transfer operation begins with the master device driving a start condition on the bus and ends with the master device driving a stop condition on the bus. The bus uses transitions on the data pin (SDA) while the clock (SCL) is "HIGH" to indicate start and stop conditions. A high-to-low transition on SDA indicates a start and a low-to-high transition indicates a stop. Normal data-bit transitions must occur within the low time of the clock period. These conditions are shown in 图 28. The master generates the 7-bit slave address and the read/write (R/W) bit to open communication with another device and then waits for an acknowledge condition. The TAS5722L device holds SDA "LOW" during the acknowledge clock period to indicate an acknowledgment. When the hold occurs, the master transmits the next byte of the sequence. All compatible devices share the same signals via a bidirectional bus using a wired-AND connection. An external pull-up resistor must be used for the SDA and SCL signals to set the "HIGH" level for the bus.

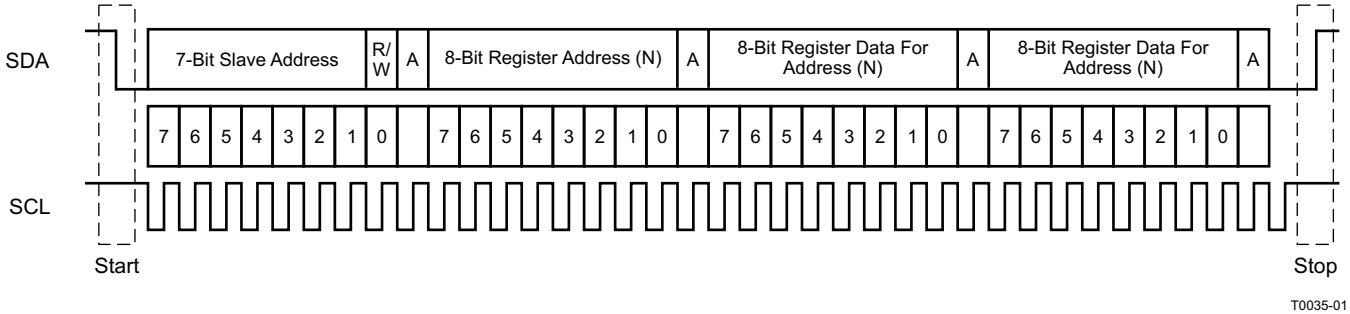


图 28. Typical I²C Timing Sequence

The number of bytes that can be transmitted between start and stop conditions is unlimited. When the last word transfers, the master generates a stop condition to release the bus. A generic data transfer sequence is shown in 图 28.

版权 © 2016, Texas Instruments Incorporated

7.3.2.1 Writing to the I²C Interface

As shown 图 29, a single-byte data-write transfer begins with the master device transmitting a start condition followed by the I²C bit and the read/write bit. The read/write bit determines the direction of the data transfer. For a data-write transfer, the read/write bit is a 0. After receiving the correct I²C bit and the read/write bit, the TAS5722L device responds with an acknowledge bit. Next, the master transmits the address byte corresponding to the TAS5722L device register being accessed. After receiving the address byte, the TAS5722L device again responds with an acknowledge bit. Next, the master device transmits the data byte to be written to the memory address being accessed. After receiving the data byte, the TAS5722L device again responds with an acknowledge bit. Finally, the master device transmits a stop condition to complete the single-byte data-write transfer.

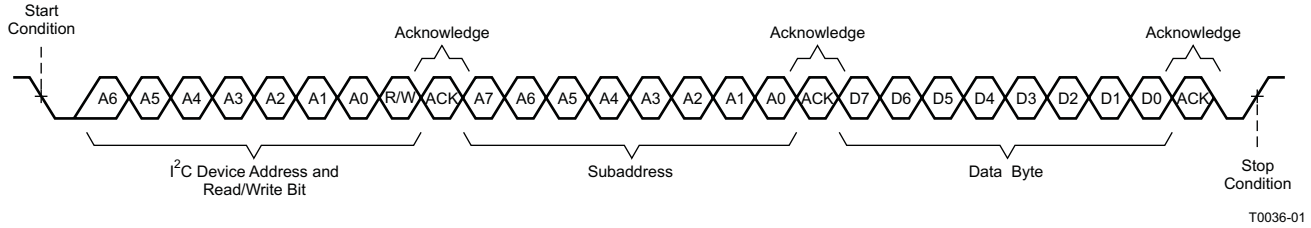


图 29. Single Byte Write Transfer Timing

A multi-byte data write transfer is identical to a single-byte data write transfer except that multiple data bytes are transmitted as shown in 图 30. After receiving each data byte, the TAS5722L device responds with an acknowledge bit. Sequential data bytes are written to sequential addresses.

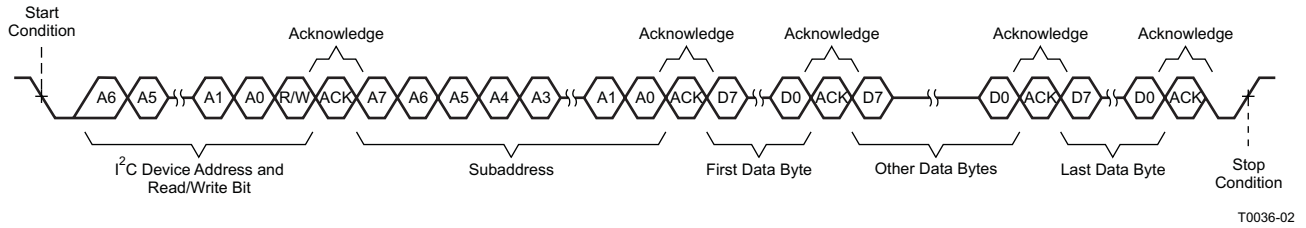


图 30. Multi-Byte Write Transfer Timing

7.3.2.2 Reading from the I²C Interface

As shown in 图 30, a data-read transfer begins with the master device transmitting a start condition, followed by the I² device address and the read/write bit. For the data read transfer, both a write followed by a read are actually done. Initially, a write is done to transfer the address byte of the internal register to be read. As a result, the read/write bit becomes a 0. After receiving the TAS5722L device address and the read/write bit, TAS5722L device responds with an acknowledge bit. In addition, after sending the internal memory address byte or bytes, the master device transmits another start condition followed by the TAS5722L device address and the read/write bit again. Then the read/write bit becomes a 1, indicating a read transfer. After receiving the address and the read/write bit, the TAS5722L device again responds with an acknowledge bit. Next, the TAS5722L device transmits the data byte from the register being read. After receiving the data byte, the master device transmits a not-acknowledge followed by a stop condition to complete the data-read transfer.

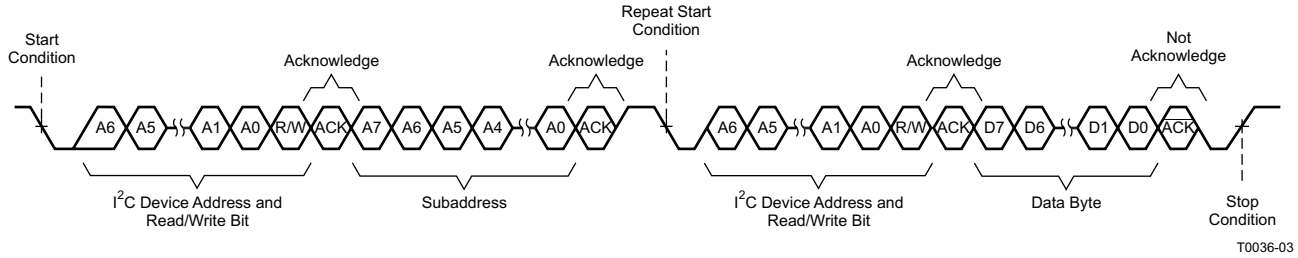


图 31. Single Byte Read Transfer Timing

A multiple-byte data read transfer is identical to a single-byte data read transfer except that multiple data bytes are transmitted by the TAS5722L to the master device as shown 图 32. Except for the last data byte, the master device responds with an acknowledge bit after receiving each data byte.

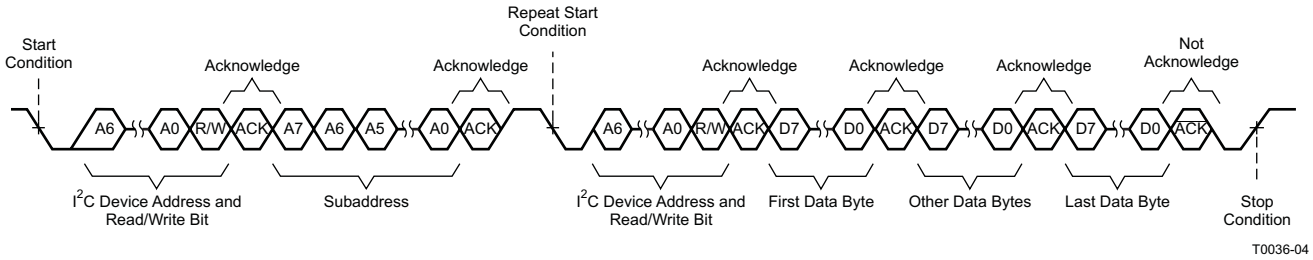


图 32. Multi-Byte Read Transfer Timing

版权 © 2016, Texas Instruments Incorporated

7.3.3 Serial Audio Interface (SAIF)

The TAS5722L device SAIF supports a variety of standard stereo serial audio formats including I^2S, Left Justified and Right Justified. It also supports a time division multiplexed (TDM) format that is capable of transporting up to 8 channels of audio data on a single bus. LRCLK and SDIN are sampled on the rising edge of BCLK.

For the stereo formats (I^2S, Left Justified and Right Justified), the TAS5722L device supports BCLK to LRCLK ratios of 32, 48 and 64. If the BCLK to LRCLK ratio is 64, MCLK can be derived from BCLK internally. The MCLK_PIN_CFG bit (register 0x13, bit 1) controls the source of MCLK and by default derives MCLK from an internal version of BCLK. In this case connect the MCLK pin to a valid logic low value.

If the BCLK to LRCLK ratio is 32 or 48, MCLK must be externally driven. The valid MCLK to LRCLK ratios are 64, 128, 256 and 512 as long as the frequency of MCLK is 37 MHz or less. If the BCLK to LRCLK ratio is 64, it is also acceptable to connect BCLK to MCLK and set the MCLK_PIN_CFG bit high.

For TDM operation, the TAS5722L device supports 4 and 8 times slots at both single speed (44.1 kHz or 48 kHz) and double speed (88.2/96 kHz) sample rates. 表 2 lists the supported TDM frame configurations. For 16 and 32-bits per TDM slot, MCLK can be connected to BCLK internally by leaving the MCLK_PIN_CFG bit (register 0x13, bit 1) to its default value of 0. For 24-bit time slot operation, MCLK must be externally driven with a valid ratio of 64, 128, 256 or 512 as long as MCLK is less than 37 MHz.

表 2. TDM Frame Configurations

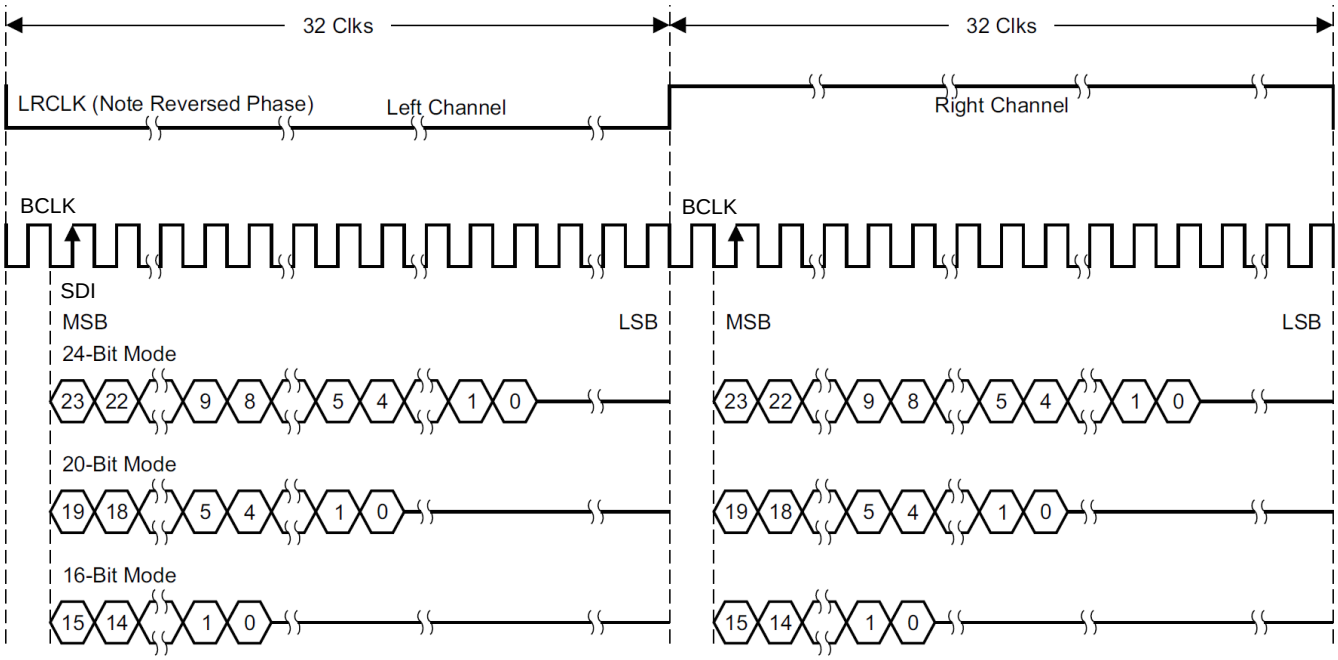
SAMPLE RATE (kHz)	TDM SLOTS	BITS PER TDM SLOT	SUPPORTED	MCLK = BCLK	TDM_SLOT_16B
44.1/48	4	16	Yes	Yes	1
		24	Yes	No	0
		32	Yes	Yes	0
	8	16	Yes	Yes	1
		24	Yes	No	0
		32	Yes	Yes	0
88.2/96	4	16	Yes	Yes	1
		24	Yes	No	0
		32	Yes	Yes	0
	8	16	Yes	Yes	1
		24	Yes	No	0
		32	Yes	Yes	0

If 16-bit time slots are utilized, set the TDM_SLOT_16B register bit (register 0x13, bit 2) to a 1. The SAIF auto detects 24-bit vs. 32-bit time slot widths if TDM_SLOT_16B is set to a 0.

The TAS5722L device selects the channel for playback based on either its I^2C base address offset or based on a dedicated time slot selection register. See the *Adjustable I^2C Address* section for more information.

7.3.3.1 Stereo I²S Format Timing

illustrates the timing of the stereo I²S format with 64 BCLK per LRCLK. Two's complement data is transmitted MSB to LSB with the left channel word beginning one BCLK after the falling edge of LRCLK and the right channel beginning one BCLK after the rising edge of LRCLK. Since data is MSB aligned to the beginning of word transmission, data precision does not need to be configured. Set the SAIF_FORMAT[2:0] register bits to I²S (register 0x02, bits 2:0 = 3'b100).



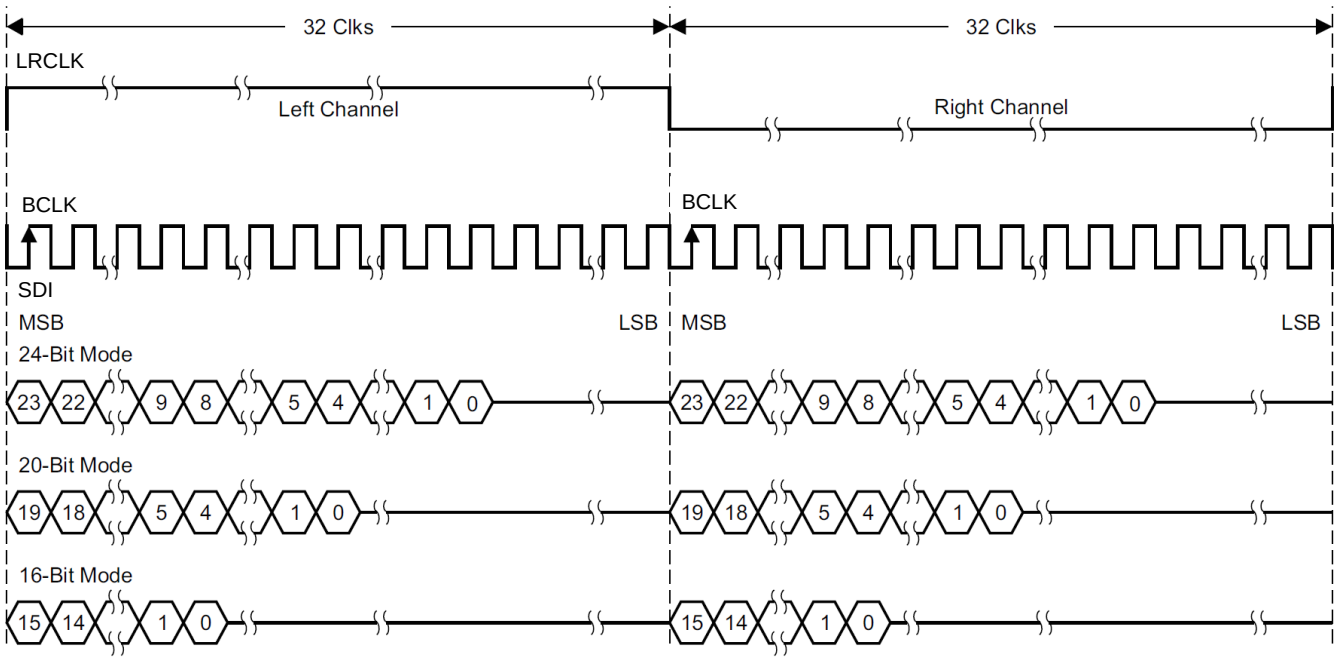
A. Data presented in two's-complement form with most significant bit (MSB) first.

图 33. I²S 64-f_S Format

版权 © 2016, Texas Instruments Incorporated

7.3.3.2 Stereo Left-Justified Format Timing

The stereo left justified format is very similar to the I^2S format timing, except the data word begins transmission at the same cycle that LRCLK toggles (when it is shifted by one bit from I^2S). The phase of LRCLK is also opposite of I^2S. The left channel begins transmission when LRCLK transitions from low to high and the right channel begins transmission when LRCLK transitions from high-to-low. Set the SAIF_FORMAT[2:0] register bits to left-justified (register 0x02, bits 2:0 = 3'b101).The timing is illustrated in .



A. Data presented in two's-complement form with most significant bit (MSB) first.

图 34. Left-Justified 64-f_S Format

7.3.3.3 Stereo Right-Justified Format Timing

The stereo right justified format aligns the LSB of left channel data to the high to low transition of LRCLK and the LSB of the right channel data to the low to high transition of LRCLK. To insure data is received correctly, the SAIF must be configured for the proper data precision. The TAS5722L supports 16, 18, 20 and 24-bit data precision in right justified format. Set the SAIF_FORMAT[2:0] register bits (register 0x02, bits 2:0) to the appropriate right-justified setting based on bit precision (value = 3'b000 for 24-bit, 3'b001 for 20-bit, 3'b010 for 18-bit and 3'b011 for 16-bit). The timing is illustrated in .

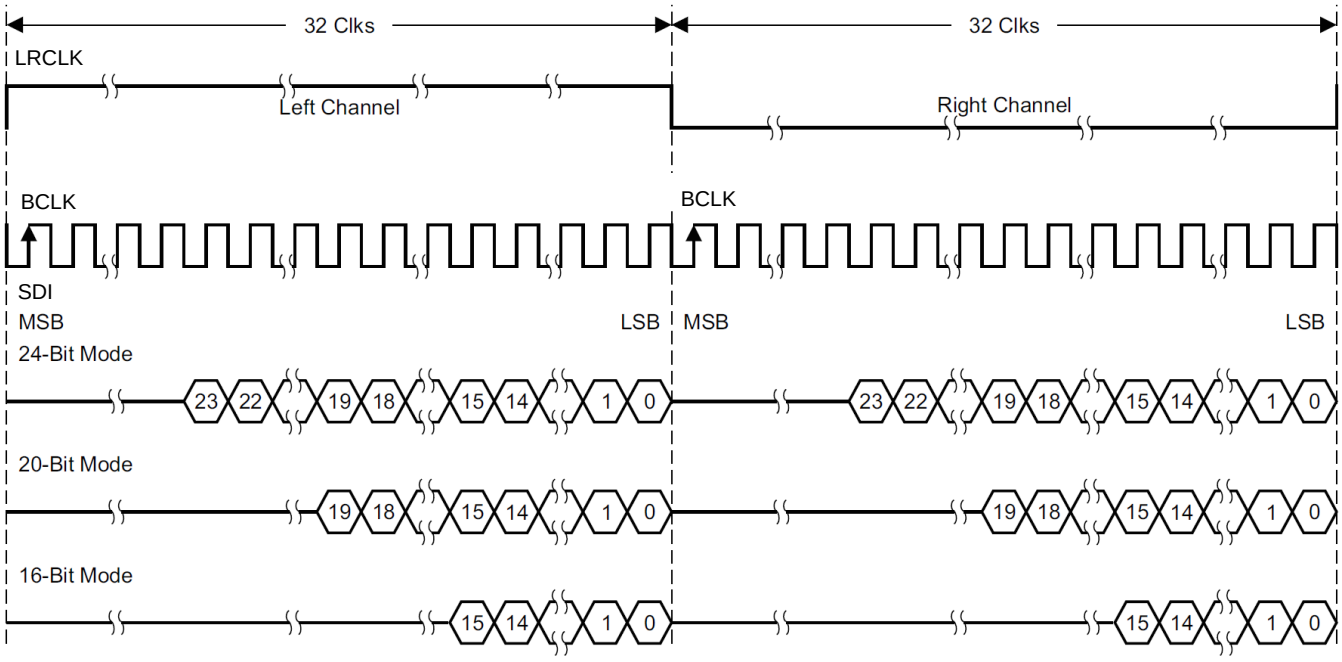


图 35. Right-Justified 64-f_S Format

版权 © 2016, Texas Instruments Incorporated

7.3.3.4 TDM Format Timing

A TDM frame begins with the low to high transition of LRCLK. As long as LRCLK is high for at least one BCLK period and low for one BCLK period, duty cycle is irrelevant. The SAIF automatically detects the number of time slots as long as valid BCLK to LRCLK ratios are utilized (see SAIF introduction above).

For I^2S aligned TDM operation (when time slot 0 begins, one clock cycle after the low to high transition of LRCLK), set SAIF_FORMAT[2:0] register bits to I^2S (register 0x02, bits 2:0 = 3'b100). Data is MSB aligned within the 32-bit time slots, so data precision does not need to be configured. The TDM format timing is illustrated in .

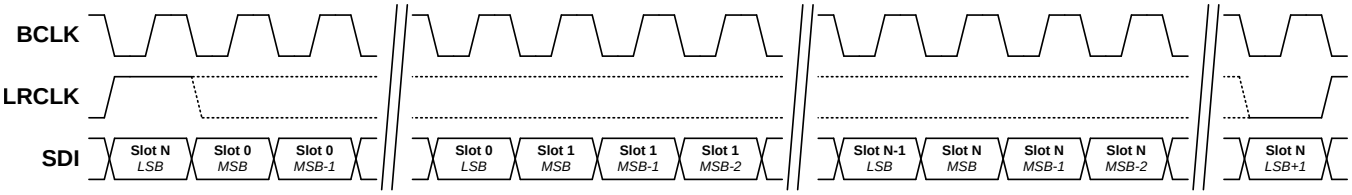


图 36. TDM I^2S Format

For left-justified TDM operation (when time slot 0 begins the cycle LRCLK transitions from low to high), set SAIF_FORMAT[2:0] register bits to left-justified(register 0x02, bits 2:0 = 3'b101). As with I^2S, data is MSB aligned. The timing is illustrated in .

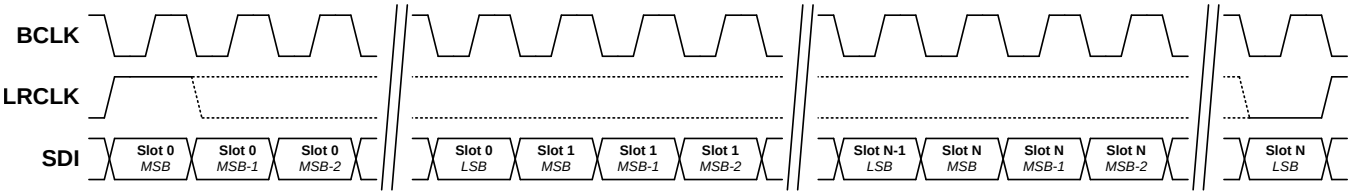


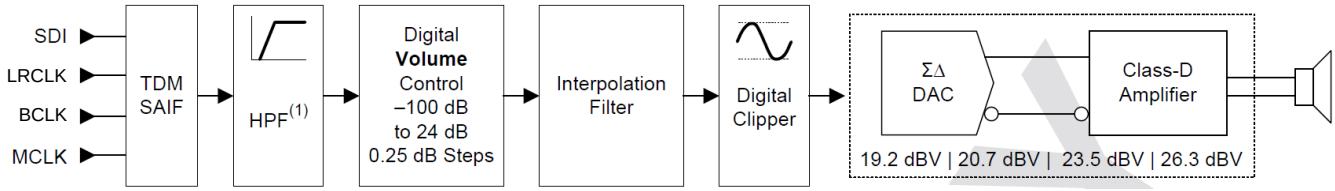
图 37. TDM Left- and Right-Justified Format

For right-justified TDM operation (when time slot 0 begins the cycle LRCLK transitions from low to high), data is LSB aligned to the 32-bit time slot. As with stereo right-justified formats, the TAS5722L must have the data precision configured. Set the SAIF_FORMAT[2:0] register bits (register 0x02, bits 2:0) to the appropriate right-justified setting based on bit precision (value = 3'b000 for 24-bit, 3'b001 for 20-bit, 3'b010 for 18-bit and 3'b011 for 16-bit). The timing shown in is the same as left-justified TDM, with the data LSB aligned.

版权 © 2016, Texas Instruments Incorporated

7.3.4 Audio Signal Path

illustrates the audio signal flow from the TDM SAIF to the speaker.



(1) See 表 3 for frequency options.

图 38. Audio Signal Path

7.3.4.1 High-Pass Filter (HPF)

Excessive DC in audio content can damage loudspeakers, so the amplifier employs a DC detect circuit that shuts down the power stage and issues a latching fault if this condition occurs. A high-pass filter is provided in the TAS5722L device to remove DC from incoming audio data to prevent this from occurring. 表 3 shows the high-pass, –3 dB corner frequencies for each sample rate. The filter can be bypassed by writing a 1 into bit 7 of register 0x02. The high pass corner frequency can be adjusted by setting the HPF_CORNER bits in the Digital Control 3 register (B[5:7], register 0x13).

表 3. High-Pass Filter –3 dB Corner Frequencies by Sample Rate

SAMPLE RATE (kHz)	-3dB CORNER FREQUENCY (Hz) vs. HPF_CORNER [2:0]							
	000	001	010	011	100	101	110	111
44.1	3.675	7.35	14.7	29.4	58.8	117.6	235.2	470.4
48	4	8	16	32	64	128	256	512
88.2	7.35	14.7	29.4	58.8	117.6	235.2	470.4	940.8
96	8	16	32	64	128	256	512	1024

7.3.4.2 Amplifier Analog Gain and Digital Volume Control

The gain from TDM SAIF to speaker is controlled by setting the amplifier's analog gain and digital volume control. Amplifier analog gain settings are presented as the output level in dBV (dB relative to 1 Vrms) with a full scale serial audio input (0 dBFS) and the digital volume control set to 0 dB. It should be noted that these levels may not be achievable because of analog clipping in the amplifier, so they should be used to convey gain only.

表 4 outlines each gain setting expressed in dBV and V_{PK}.

表 4. Amplifier Gain Settings

ANALOG_GAIN [1:0] SETTING	FULL SCALE OUTPUT	
	dBV	V_{PEAK} (V)
00	19.2	12.9
01	20.7	15.3
10	23.5	21.2
11	26.3	29.2

公式 1 calculates the amplifiers output voltage.

$$V_{AMP} = \text{Input} + A_{dvc} + A_{AMP} \quad \text{dBV} \tag{1}$$

where

- V_{AMP} is the amplifier output voltage in dBV
- Input is the digital input amplitude in dB with respect to 0 dBFS
- A_{dvc} is the digital volume control setting, –100 dB to 24dB in 0.25-dB steps
- A_{AMP} is the amplifier analog gain setting (19.2, 20.7, 23.5, or 26.3) in dBV

版权 © 2016, Texas Instruments Incorporated

Clipping in the digital domain occurs if the input level (in dB relative to 0 dBFS) plus the digital volume control setting (in dB) are greater than 0 dB. The signal path has approximately 0.5 dB of headroom, but TI does not recommend utilizing it.

The digital volume control (DVC) can be adjusted from –100 dB to 24 dB in 0.25-dB steps. 公式 2 illustrates how to set the 9-bit volume control bits. The top 8 MSBs of the DVCvalue are stored in Volume Control register (register 0x04) and the LSB is stored in the Digital Control 3 register (register 0x13, bit 0).

$$DVC_{value} = 0x19E + \frac{A_{dvc}}{0.25} \quad (2)$$

For example, digital volume settings of 0 dB, 24 dB and –100 dB map to 0x19E, 0x1FE and 0x0E respectively. Values below 0x0E are equivalent to mute (the amplifier continues to switch with no audio). When a change in digital volume control occurs, the device ramps the volume to the new setting in 0.25 dB steps either every LRCLK or every 8 LRCLK depending on the value of the VOL_RAMP_RATE bit (bit 6, reg 0x03).

The Class-D amplifier uses a closed-loop architecture, so the gain does not depend on the supply input (V_{PVDD}). The approximate threshold for the onset of analog clipping is calculated in 公式 3.

$$V_{PK(max,preclip)} = V_{PVDD} \times \left(\frac{R_L}{2 \times R_{DS(on)} + R_{interconnect} + R_L} \right) V \quad (3)$$

where

- $V_{PK(max,preclip)}$ is the maximum peak unclipped output voltage in V
- V_{PVDD} is the power supply voltage
- R_L is the speaker load in Ω
- $R_{interconnect}$ is the additional resistance in the PCB (such as cabling and filters) in Ω
- $R_{DS(on)}$ is the power stage total on resistance (FET+bonding+packaging) in Ω

The effective on-resistance for the device (including FETs, bonding and packaging leads) is approximately 150 mΩ at room temperature and increases by approximately 1.6 times over +100°C rise in temperature.表 5 shows approximate maximum unclipped peak output voltages at room temperature (excluding interconnect resistances).

表 5. Approximate Maximum Unclipped Peak Output Voltage at Room Temperature

SUPPLY VOLTAGE V_{PVDD} (V)	MAXIMUM UNCLIPPED PEAK VOLTAGE V_{PK} (V)	
	R_L = 4 Ω	R_L = 8 Ω
12	11.16	11.57
17	15.81	16.39

7.3.4.3 Digital Clipper

The digital clipper hard limits the maximum DAC sample value, which provides a simple hardware mechanism to control the largest signal applied to the speaker. Because the block resides in the digital domain, the actual maximum output voltage also depends on the amplifier gain setting and the supply voltage (V_{PVDD}) limited amplifier voltage swing (For example, analog clipping may occur before digital clipping).

The maximum amplifier output voltage (excluding limitation due to swing) is calculated in 公式 4.

$$V_{AMP(max,dc)} = 20 \times \log_{10} \left(\frac{DC_{level}}{0xFFFFF} \right) + 0.5 + A_{AMP} \quad (4)$$

where

- $V_{AMP(max,dc)}$ is the amplifier maximum output voltage in dBV
- DC_{level} is the digital clipper level
- A_{AMP} is the amplifier analog gain setting (19.2, 20.7, 23.5, or 26.3) in dBV

Configure the digital clipper by writing the 20-bit DC_{level} to registers 0x01, 0x10 and 0x11. Set the DC_{level} to 0xFFFFF effectively bypasses the digital clipper.

7.3.4.4 Class-D Amplifier Settings

The PWM switching rate of the Class-D amplifier is a phase locked multiple of the input audio sample rate. 表 6 lists the PWM switching rate settings as programmed in bit 4 through bit 6 in register 0x06. The double-speed sample rates (for example 88.2 kHz, 96 kHz) have the same PWM switching frequencies as their equivalent single-speed sample rates.

表 6. PWM Switching Rates

PWM_RATE [2:0]	SINGLE-SPEED PWM RATE (× f_{LRCLK})	DOUBLE-SPEED PWM RATE × f_{LRCLK})	44.1 kHz, 88.2 kHz f_{PWM}(kHz)	48 kHz, 96 kHz f_{PWM}(kHz)
000	6	3	264.6	288
001	8	4	352.8	384
010	10	5	441	480
011	12	6	529.2	576
100	14	7	617.4	672
101	16	8	705.6	768
110	20	10	882	960
111	24	12	1058.4	1152

The Class-D power stage overcurrent detector issues a latching fault if the load current exceeds the safe limit for the device. This threshold can be proportionately adjusted if desired by programming bits 4-5 of register 0x08. 表 7 shows the relative setting for each overcurrent setting.

表 7. Overcurrent Threshold Settings

OC_THRESH [1:0]	OVERCURRENT THRESHOLD (%)
00	100
01	75
10	50
11	25

版权 © 2016, Texas Instruments Incorporated

7.4 Device Functional Modes

This section describes the modes of operation for the TAS5722L device.

表 8. Typical Current Consumption(1)

INPUT VOLTAGE V_{PVDD} (V)	MODE	PWM FREQUENCY f_{PWM} (kHz)	$I_{PVDD}+I_{AVDD}$ (mA)	INPUT CURRENT I_{DVDD} (mA)
5	Idle and Mute	384	11.45	1.30
		480	12.21	
		576	12.94	
		672	13.70	
		768	14.41	
	Sleep	—	8.48	0.32
	Shutdown	—	0.021	0.046
12.5	Idle and Mute	384	13.06	1.30
		480	14.46	
		576	15.79	
		672	17.18	
		768	18.49	
	Sleep	—	7.49	0.32
	Shutdown	—	0.042	0.046
16.5	Idle and Mute	384	14.00	1.30
		480	15.60	
		576	17.10	
		672	18.66	
		768	20.15	
	Sleep	—	7.61	0.32
	Shutdown	—	0.045	0.046

(1) T_A = 25ºC, PVDD pin tied to AVDD pin, V_{DVDD} = 1.8 V, R_{LOAD} = 4Ω + 33 µH, f_{IN} = Idle, f_S = 48 kHz, Gain = 20.7 dBV, PWR_TUNE bit = 1

7.4.1 Shutdown Mode (SDZ)

The device enters shutdown mode if either the SDZ pin is asserted low or the I^2C SDZ register bit is set low (bit 0, reg 0x01). In shutdown mode, the device consumes the minimum quiescent current with most analog and digital blocks powered down. The Class-D amplifier power stage powers down and the output pins are in a Hi-Z state. I^2C communication remains possible in shutdown mode and register bits states are retained.

If a latching fault condition has occurred (Over Temperature, Over Current or DC detect), the SDZ pin or I^2C bit must toggle low before the fault register can be cleared. For more information on faults and recovery, see the *Faults and Status* section.

When the device exits shutdown mode (either by releasing the SDZ pin high or setting the I^2C SDZ register bit high), the device powers up the internal analog and digital blocks required for operation. If the I^2C SLEEP bit is set low (bit 1, reg 0x01), the device powers up the Class-D amplifier and begins the switching of the power stage. If the I^2C MUTE bit is set low (bit 4, reg 0x03), the device ramps up the volume to the current setting and begins playing audio.

If shutdown mode is asserted while audio is playing, the device ramps down the volume on the audio, stops the Class-D switching, puts the Class-D power stage output pins in a Hi-Z state and powers down the analog and digital blocks.

7.4.2 Sleep Mode

Sleep mode is similar to shutdown mode, except analog and digital blocks required to begin playing audio quickly remain powered up. Sleep mode operates as a *hard mute* where the Class-D amplifier stops switching, but the device does not power down completely. Entering sleep mode does not clear latching faults.

版权 © 2016, Texas Instruments Incorporated

7.4.3 Mode Timing

When SDZ is deasserted (and the device is not in sleep mode), the amplifier begins to switch after a period of t_{ACTIVE}. At this point, the volume ramps from –100 dB to the programmed digital volume control (DVC) setting in a length of time t_{VRMP}. t_{VRMP} is determined by the DVC setting, sample rate and volume ramp rate bit, VOL_RAMP_RATE (bit 6 of register 0x03). Ramping the volume prevents audible artifacts that can occur if discontinuous volume changes are applied while audio is being played back. This period, t_{VRMP}, depends on the DVC setting and sample rate. Typical values for t_{VRMP} for a DVC of 0 dB are shown in Timing Requirements. 图 4 illustrates mode timing.

The time to enter or exit sleep or mute and the time to enter shudown are dominated by t_{VRMP}. 表 9 lists the timing parameters based on t_{VRMP}.

表 9. Typical DVC Ramp Times

SAMPLE RATE (kHz)	RAMP TIMES (t_{VRAMP}) FROM –100 dB to 0 dB (ms)	
	VOL_RAMP_RATE = 0	VOL_RAMP_RATE = 1
44.1	72.6	9.1
48	66.7	8.3
88.2	36.3	4.5
96	33.3	4.2

7.4.4 Auto Sleep Mode

Auto sleep mode is an optional feature that automatically moves the amplifier from active mode to sleep mode when the device presents an idle audio input (i.e. zero value) to the SAIF for a prescribed number of samples. The device automatically returns to active mode when the device presents a non-idle audio input sample to the SAIF. Auto sleep mode takes advantage of the TAS5722L device's ability to rapidly enter and exit sleep mode from active mode. Because the device applies idle audio samples to the SAIF before entering sleep mode, a volume ramp can be avoided. When exiting sleep mode, the amplifier can resume switching before input sample has propagated through the signal path, which avoids any audible artifacts when resuming playback. AUTO_SLEEP[1:0] (bits 4:3 in register 0x13) configures the number of idle samples required to enter auto sleep.

7.4.5 Active Mode

If shutdown mode and sleep mode are not asserted, the device is in active mode. During active mode, audio playback is enabled.

7.4.6 Mute Mode

When the I^2C_MUTE bit is set high (bit 4, reg 0x03) and the device is in active mode, the volume is ramped down and the Class-D amplifier continues to operate with an idle audio input.

7.4.7 Faults and Status

During the power-up sequence, the power-on-reset circuit (POR) monitoring the DVDD pin domain releases all registers from reset (including the I^2C registers) once DVDD is valid. The device does not exit shutdown mode until the PVDD pin has a valid voltage between the undervoltage lockout (UVLO) and overvoltage lockout (OVLO) thresholds. If DVDD drops below the POR threshold the device transitions into shutdown mode with all registers held in reset. If UVLO or OVLO thresholds are violated by PVDD, the device transitions into sleep mode, but registers are not forced into reset. Both of these conditions are non-latching and the device operates normally once supply voltages are valid again. The device can be reset only by reducing DVDD below the POR threshold.

The device transitions into sleep mode if it detects any faults with the SAIF clocks such as

- Invalid MCLK to LRCLK and BCLK to LRCLK ratios
- Invalid MCLK and LRCLK frequencies
- Halting of MCLK, BCLK or LRCLK clocks

版权 © 2016, Texas Instruments Incorporated

Upon detection of a SAIF clock error, the device transitions into sleep mode as quickly as possible to limit the possibility of audio artifacts. Once all SAIF clock errors are resolved, the device volume ramps back to its previous playback state. During an SAIF clock error, the FAULTZ pin asserts low and the CLKE bit asserts high (register 0x08, bit 3).

While operating in shutdown mode, the SAIF clock error detect circuitry powers down and the CLKE bit reads high. This reading is not an indication of a SAIF clock error. If the device has not entered active mode after a power-up sequence or after transitioning out of shutdown mode, the FAULTZ pin pulses low for only approximately 10 µs every 350 µs. This action prevents a possible locking condition if the FAULTZ is connected to the SDZ pin to accomplish automatic recovery. Once the device has entered active mode one time (after power up or deassertion of shutdown mode), the SAIF clock errors pull the FAULTZ pin low continuously until the fault has cleared.

The device also monitors die temperature, power stage load current and amplifier output DC content and issues latching faults if any of these conditions occur. A die temperature of approximately 150°C causes the device to enter sleep mode and issue an over-temperature error (OTE) readable via I^2C (bit 0, reg 0x08).

Sustained excessive DC content at the output of the Class-D amplifier can damage loudspeakers via voice coil heating. The amplifier has an internal circuit to detect significant DC content that forces the device into sleep mode. The device issues a DC detect error (DCE) readable via I^2C (bit 1, reg 0x08).

If the Class-D amplifier load current exceeds the threshold set by the OC_THRESH register bits (bits 5-4, reg 0x08), the device enters sleep mode and issues an overcurrent error (OCE) that is readable via I^2C (bit 2, reg 0x08).

During OTE, DCE and OCE, the FAULTZ pin asserts low until the latched fault is cleared. FAULTZ is an open drain pin and requires a pull-up resistor to the DVDD pin to achieve a logic high level when no faults exist. This can be accomplished either with an internal pull up asserting FAULTZ_PU high (register 0x14, bit 3) or with an external pull up resistor to DVDD.

Latched faults can be cleared only by toggling the SDZ pin or SDZ I^2C bit (bit 0, reg 0x01). This toggle does not clear I^2C registers (except the fault status of OTE, OCE and DCE). If it is desirable for the device to attempt automatic recovery after latching faults, implement a circuit like the one shown in . The device waits approximately 650 ms after a DCE fault has cleared and 1.3 s after an OTE or OCE fault has cleared before releasing FAULTZ high and allowing the device to enter active mode.

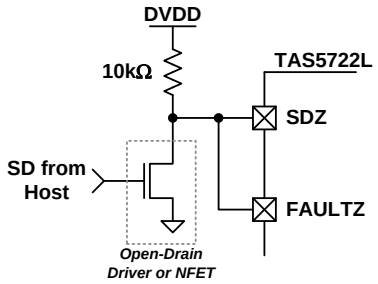


图 39. Auto Recovery Circuit

7.5 Register Maps

When writing to registers with reserved bits, maintain the values shown in 表 10 to ensure proper device operation. Default register values are loaded during the power-up sequence or any time the DVDD voltage falls below the power-on-reset (POR) threshold and then returns to valid operation.

7.5.1 I²C Register Map Summary

表 10. I²C Register Map Summary

ADDR (Dec)	ADDR (Hex)	REGISTER NAME	REGISTER BITS								DEFAULT (Hex)
			B7	B6	B5	B4	B3	B2	B1	B0	
0	0x00	Device ID	DEVICE_ID								0x12
			0	0	0	1	0	0	1	0	
1	0x01	Power Control	DIGITAL_CLIP_LEVEL [19:14]						SLEEP	SDZ	0xFD
			1	1	1	1	1	1	0	1	
2	0x02	Digital Control 1	HPF_BYPASS	TDM_CFG_SRC	RSV		SSZ/DS	SAIF_FORMAT			0x04
			0	0	0	0	0	1	0	0	
3	0x03	Digital Control 2	RSV	VOL_RAMP_RATE	RSV	MUTE	RSV	TDM_SLOT_SELECT[2:0]			0x80
			1	0	0	0	0	0	0	0	
4	0x04	Volume Control	VOLUME_CONTROL [8:1]								0xCF
			1	1	0	0	1	1	1	1	
6	0x06	Analog Control	RSV	PWM_RATE			ANALOG_GAIN		RSV		0x51
			0	1	0	1	0	0	0	1	
8	0x08	Fault Config and Error Status	RSV		OC_THRESH		CLKE	OCE	DCE	OTE	0x00
			0	0	0	0	0	0	0	0	
16	0x10	Digital Clipper 2	DIGITAL_CLIP_LEVEL[13:6]								0xFF
			1	1	1	1	1	1	1	1	
17	0x11	Digital Clipper 1	DIGITAL_CLIP_LEVEL[5:0]						RSV		0xFC
			1	1	1	1	1	1	0	0	
19	0x13	Digital Control 3	HPF_CORNER			AUTO_SLEEP		TDM_SLOT_16B	MCLK_PIN_CFG	VOL_CONTROL[0]	0x00
			0	0	0	0	0	0	0	0	
20	0x14	Analog Control 2	RSV				FAULTZ_PU	VREG_LVL	RSV	PWR_TUNE	0x02
			0	0	0	0	0	0	1	0	

版权 © 2016, Texas Instruments Incorporated

7.5.2 Register Maps

7.5.2.1 Device Identification Register (0x00)

图 40. Device Identification Register

7	6	5	4	3	2	1	0
DEVICE_ID[7:0]							
R							

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 11. Device Identification Register Field Descriptions

Bit	Field	Type	Reset	Description
7-0	DEVICE_ID[7:0]	R	0	This register returns a value of 0x12 when read.

7.5.2.2 Power Control Register (0x01)

图 41. Power Control Register

7	6	5	4	3	2	1	0
DIGITAL_CLIP_LEVEL[19:14]						SLEEP	SDZ
R/W						R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 12. Power Control Register Field Descriptions

Bit	Field	Type	Reset	Description
7-2	DIGITAL_CLIP_LEVEL[19:14]	R/W	1	This register holds the top 6-bits of the 20-bit Digital Clipper level. The Digital Clipper limits the magnitude of the sample applied to the DAC. See the *Digital Clipper* section for more information.
1	SLEEP	R/W	0	When the device enters SLEEP mode, volume ramps down and the Class-D output stage powers down to a Hi-Z state. The rest of the blocks maintain a state such that audio playback can be restarted as quickly as possible. This mode has lower dissipation than MUTE, but higher than SHUTDOWN. For more information see the *Device Functional Modes* section. 0: Exit Sleep (default). 1: Enter Sleep.
0	SDZ	R/W	1	The device enters SHUTDOWN mode if either this bit is set to a 0 or the SDZ pin is pulled low externally. In SHUTDOWN, the device holds the lowest dissipation state. I^2C communication remains functional and all registers are retained. For more information see the *Device Functional Modes* section. 0: Enter SHUTDOWN. 1: Exit SHUTDOWN (default).

7.5.2.3 Digital Control Register 1 (0x02)

图 42. Digital Control Register 1

7	6	5	4	3	2	1	0
HPF_BYPASS	TDM_CFG_SRC	Reserved		SSZ/DS	SAIF_FORMAT[2:0]		
R/W	R/W	R/W		R/W	R/W		

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 13. Digital Control Register 1 Field Descriptions

Bit	Field	Type	Reset	Description
7	HPF_BYPASS	R/W	0	The high-pass filter removes any DC component in the audio content that could trip the DC detect protection feature in the amplifer, which is a latching fault. Setting this bit bypasses the high-pass filter. See the "High-Pass Filter" section under "Audio Signal Path" for more information. 0: Enable high-pass filter (default). 1: Bypass high-pass filter.
6	TDM_CFG_SRC	R/W	0	This bit determines how the device selects which audio channel direct to the playback stream. See the *Serial Audio Interface (SAIF)* section for more information. 0: Set TDM Channel to I^2C Device ID (default). 1: Set TDM Channel to TDM_SLOT_SELECT in register 0x03.
5-4	Reserved	R/W	0	These bits are reserved and should be set to 00 when writing to this register.
3	SSZ/DS	R/W	0	This bit sets the sample rate to single speed or double speed operation. See the *Serial Audio Interface (SAIF)* section for more information. 0: Single speed operation (44.1 kHz/48 kHz) - default. 1: Double speed operation (88.2 kHz/96 kHz)
2-0	SAIF_FORMAT[2:0]	R/W	100	These bits set the Serial Audio Interface format. See the *Serial Audio Interface (SAIF)* section for more information. 000: Right justified, 24-bit 001:Right justified, 20-bit 010: Right justified, 18-bit 011: Right justified, 16-bit 100: I^2S (default) 101: Left Justified, 16-24 bits 110: Reserved. Do not select this value. 111: Reserved. Do not select this value.

7.5.2.4 Register Name (offset =) [reset =] or (address =) [reset =]

图 43. 8-bit, 1 Row

7	6	5	4	3	2	1	0
Reserved	VOL_RAMP_RATE	Reserved	MUTE	Reserved	TDM_SLOT_SELECT[2:0]		
R/W	R/W	R/W	R/W	R/W	R/W		

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 14. (For example, CONTROL_REVISION Register) Field Descriptions

Bit	Field	Type	Reset	Description
7	Reserved	R/W	1	This bit is reserved and should be set to 1 when writing to this address
6	VOL_RAMP_RATE	R/W	0	This bit determines the volume ramp rate when entering or exiting Mute, Shutdown or Sleep 0: Ramp 0.25 dB every 8 LRCLK periods (default) 1: Ramp 0.25 dB every LRCLK period
5	Reserved	R/W	0	This bit is reserved and should be set to 1 when writing to this address

版权 © 2016, Texas Instruments Incorporated

表 14. (For example, CONTROL_REVISION Register) Field Descriptions (接下页)

Bit	Field	Type	Reset	Description
4	MUTE	R/W	0	When set the device ramps down volume and play idle audio. See the *Amplifier Analog Gain and Digital Volume Control* section for more information. 0: Exit mute mode (default). 1: Enter mute mode.
3	Reserved	R/W	0	This bit is reserved and should be set to 0 when writing to this address
2-0	TDM_SLOT_SELECT[2:0]	R/W	0	When the TDM_CFG_SRC bit is set to 1 in register 0x02, these bits select which TDM channel is directed to audio playback. See the *Serial Audio Interface (SAIF)* section for more information.

7.5.2.5 Volume Control Register (0x04)

图 44. Volume Control Register

7	6	5	4	3	2	1	0
VOLUME_CONTROL[8:1]							
R/W							

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 15. Volume Control Register Field Descriptions

Bit	Field	Type	Reset	Description
7-0	VOLUME_CONTROL[8:1]	R/W	11001111	This register sets the top 8 bits of the 9-bit Digital Volume Control (DVC), The DVC ranges from –100 dB to +24 dB in 0.25 dB steps and has a default setting of 0 dB. Register settings of less than 0x008 are equivalent to MUTE. Register 0x13 bit 0 sets the LSB value. See the *Amplifier Analog Gain and Digital Volume Control* for more information.

7.5.2.6 Analog Control Register (0x06)

图 45. Analog Control Register

7	6	5	4	3	2	1	0
Reserved	PWM_RATE[2:0]			ANALOG_GAIN[1:0]		Reserved	
R/W	R/W			R/W		R/W	

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 16. Analog Control Register Field Descriptions

Bit	Field	Type	Reset	Description
7	Reserved	R/W	0	This bit is reserved and should be set to 0 when writing to this address
6-4	PWM_RATE[2:0]	R/W	101	These bits set the PWM switching rate, which is a locked ratio of LRCLK. For more information see the *Class-D Amplifier Settings* section. 000: 6 × LRCLK (single speed), 3 × LRCLK (double speed) 001: 8 × LRCLK (single speed), 4 × LRCLK (double speed) 010: 10 × LRCLK (single speed), 5 × LRCLK (double speed) 011: 12 × LRCLK (single speed), 6 × LRCLK (double speed) 100: 14 × LRCLK (single speed), 7 × LRCLK (double speed) 101: 16 × LRCLK (single speed), 8 × LRCLK (double speed) - default 110: 20 × LRCLK (single speed), 10 × LRCLK (double speed) 111: 24 × LRCLK (single speed), 12 × LRCLK (double speed)

表 16. Analog Control Register Field Descriptions (接下页)

Bit	Field	Type	Reset	Description
3-2	ANALOG_GAIN[1:0]	R/W	01	These bits set the analog gain of the Class-D amplifer. The values shown indicate the output level with digital volume control set to 0 dB and a full scale digital input (0 dBFS). This level may not be acheivable because of analog clipping. See the *Amplifier Analog Gain and Digital Volume Control* section for more information. 00: 19.2 dBV (default) 01: 20.7 dBV 10: 23.5 dBV 11: 26.3 dBV
1-0	Reserved	R/W	01	These bits are reserved and should be set to 01 when writing to this address

7.5.2.7 Fault Configuration and Error Status Register (0x08)

图 46. Fault Configuration and Error Status Register

7	6	5	4	3	2	1	0
Reserved		OC_THRESH[1:0]		CLKE	OCE	DCE	OTE
R/W		R/W		R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 17. Fault Configuration and Error Status Register Field Descriptions

Bit	Field	Type	Reset	Description
7-6	Reserved	R/W	00	These bits are reserved and should be set to 00 when writing to this address.
5-4	OC_THRESH[1:0]	R/W	00	This register sets the Over Current detector threshold. For more information see the *Class-D Amplifier Settings* section. 00: 100% of overcurrent limit (default) 01: 75% of overcurrent limit 10: 50% of overcurrent limit 11: 25% of overcurrent limit
3	CLKE	R	0	This bit indicates the status of the SAIF clock error detector. This is a self clearning value. 0: No SAIF clock errors. 1: SAIF clock errors are present.
2	OCE	R	0	This bit indicates the status of the overcurrent error detector. This is a latching value. 0: The Class-D output stage has not experienced an over current event. 1: The Class-D output stage has experienced an over current event.
1	DCE	R	0	This bit indicates the status of the DC detector. This is a latching value. 0: The Class-D output stage has not experienced a DC detect error. 1: The Class-D output stage has experienced a DC detect error.
0	OTE	R	0	This bit indicates the status of the over temperature detector. This is a latching value. 0: The Class-D output stage has not experienced an over temperature error. 1: The Class-D output stage has experienced an over temperature error.

版权 © 2016, Texas Instruments Incorporated

7.5.2.8 Digital Clipper 2 Register (0x10)

图 47. Digital Clipper 2 Register

7	6	5	4	3	2	1	0
DIGITAL_CLIP_LEVEL[13:6]							
R/W							

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 18. Digital Clipper 2 Register Field Descriptions

Bit	Field	Type	Reset	Description
7-0	DIGITAL_CLIP_LEVEL[13:6]	R/W	1	This register holds the bits 13 through 6 of the 20-bit Digital Clipper level. The Digital Clipper limits the magnitude of the sample applied to the DAC. See the *Digital Clipper* section for more information.

7.5.2.9 Digital Clipper 1 Register (0x11)

图 48. Digital Clipper 1 Register

7	6	5	4	3	2	1	0
DIGITAL_CLIP_LEVEL[5:0]						Reserved	
R/W						R/W	

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 19. Digital Clipper 1 Register Field Descriptions

Bit	Field	Type	Reset	Description
7-2	DIGITAL_CLIP_LEVEL[5:0]	R/W	1	This register holds the bits 5 through 0 of the 20-bit Digital Clipper level. The Digital Clipper limits the magnitude of the sample applied to the DAC. See the *Digital Clipper* section for more information.
1-0	Reserved	R/W	00	These bits are reserved and should be set to 00 when writing to this register.

7.5.2.10 Digital Control Register 3 (0x13)

图 49. Digital Control Register 3

7	6	5	4	3	2	1	0
HPF_CORNER			AUTO_SLEEP		TDM_SLOT_16B	MCLK_PIN_CFG	VOL_CONTROL[0]
R/W			R/W		R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 20. Digital Control Register 3 Field Descriptions

Bit	Field	Type	Reset	Description
7-5	HPF_CORNER	R/W	0	These bits set the High Pass Filter corner frequency. Values for 44.1- kHz sample rate are shown in this table. See 表 3 in the *Audio Signal Path* section for more information. 000: 3.7-Hz High Pass Corner at 44.1-kHz Sample Rate (Default) 001: 7.4-Hz High Pass Corner at 44.1-kHz Sample Rate 010: 14.9-Hz High Pass Corner at 44.1-kHz Sample Rate 011: 29.7-Hz High Pass Corner at 44.1-kHz Sample Rate 100: 59.4-Hz High Pass Corner at 44.1-kHz Sample Rate 101: 118.4-Hz High Pass Corner at 44.1-kHz Sample Rate 110: 235.0-Hz High Pass Corner at 44.1-kHz Sample Rate 111: 463.2-Hz High Pass Corner at 44.1-kHz Sample Rate

版权 © 2016, Texas Instruments Incorporated

表 20. Digital Control Register 3 Field Descriptions (接下页)

Bit	Field	Type	Reset	Description
4-3	AUTO_SLEEP	R/W	0	These bits control the auto sleep function that disables the power stage if no audio input has been zero for a prescribed number of samples. 00: Auto Sleep Disabled (Default) 01: Auto Sleep after 1024 LRCLK's with idle input 10: Auto Sleep after 64 × 1024 LRCLK with idle input 11: Auto Sleep after 256 × 1024 LRCLK with idle input
2	TDM_SLOT_16B	R/W	0	This bit indicates the time slot bit width. 0: Each time slot is 24 or 32 bits in width (Default). 1: Each time slot is 16 bits in width.
1	MCLK_PIN_CFG	R/W	0	This bit indicates the source of MCLK. 0: MCLK signal is derived from BCLK internally. Connect MCLK pin to GND on PCB (Default). 1: MCLK signal is derived from MCLK pin.
0	VOL_CONTROL[0]	R/W	0	This is the LSB of the Digital Volume Control.

7.5.2.11 Analog Control Register 2 (0x14)

图 50. Analog Control Register 2

7	6	5	4	3	2	1	0
Reserved				FAULTZ_PU	VREG_LVL	Reserved	PWR_TUNE
R/W				R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 21. Analog Control Register 2 Field Descriptions

Bit	Field	Type	Reset	Description
7-4	Reserved	R/W	0	These bits are reserved and should be set to 0000 when writing to this register.
3	FAULTZ_PU	R/W	0	This bit controls an internal 20-kΩ pull-up resistor on the FAULTZ pin. 0: Disable pull-up resistor (Default). 1: Enable pull-up resistor.
2	VREG_LVL	R/W	0	This bit reduces the analog voltage regulator during low PVDD < 5.5-V operation. 0: Default regulator level of 5.4 V (Default). 1: Reduced regulator level of 3.9 V.
1	Reserved	R/W	1	This bit is reserved and should be set to 1 when writing to this register.
0	PWR_TUNE	R/W	0	This bit reduces static analog current in the analog domain by approximately 0.9 mA. 0: Do not reduce analog supply current (Default). 1: Reduce analog supply current.

版权 © 2016, Texas Instruments Incorporated

8 Applications and Implementation

8.1 Application Information

This section describes a filter-free,TDM application.

8.2 Typical Application

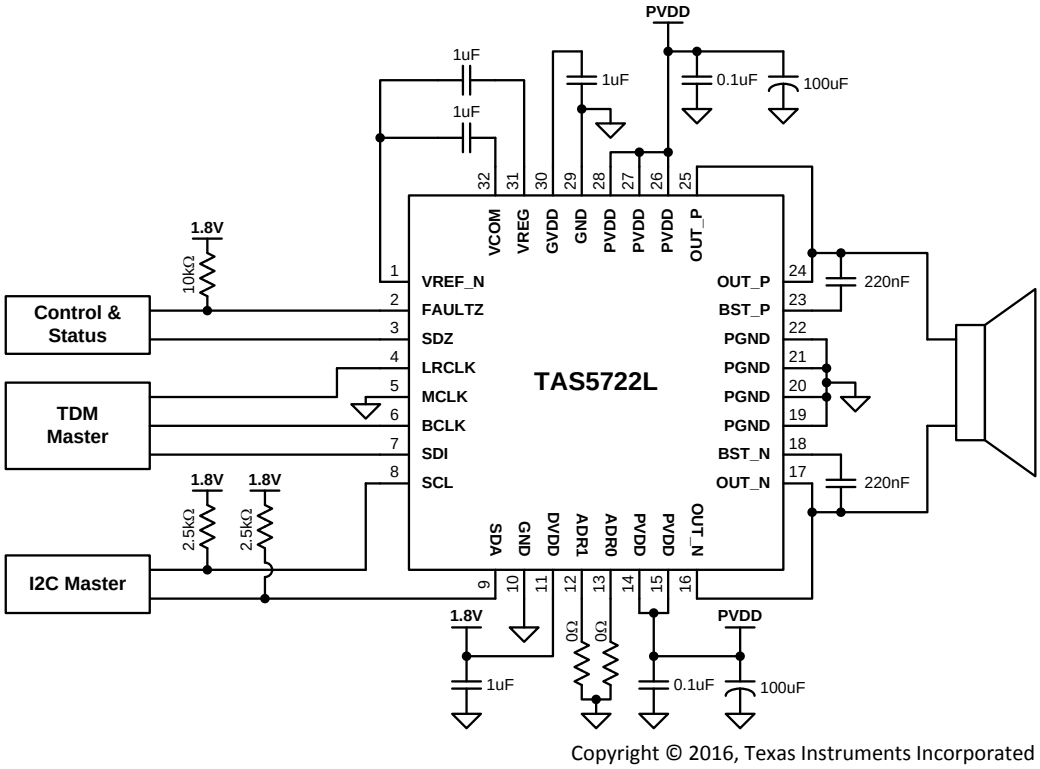


图 51. Filter Free 3-Wire TDM Application Circuit (I2C_DEV_ID = 0x6C)

8.2.1 Design Requirements

- Input voltage range PVDD and AVDD: 4.5 V to 17 V
- Input voltage range DVDD: 1.65 V to 2 V
- Input sample rate: 44.1 kHz to 48 kHz or 88.2 kHz to 96 kHz
- I^2C clock frequency: up tp 400 kHz
- Maximum output power: 15 W

8.2.2 Design Procedure

8.2.2.1 Overview

The TAS5722L is a very flexible and easy to use Class D amplifier; therefore the design process is straightforward. Before beginning the design, gather the following information regarding the audio system.

- PVDD rail planned for the design
- Speaker or load impedance
- Audio sample rate
- Maximum output power requirement
- Desired PWM frequency

Typical Application (接下页)

8.2.2.2 Select the PWM Frequency

Set the PWM frequency by writing to the PWM_RATE bits (bits 6-4, reg 0x06). The default setting for this register is 101, which is 16 × LRCLK for single speed applications and 8 × LRCLK for double speed application. This value equates to a default PWM frequency of 768 kHz for a 48 kHz sample rate.

8.2.2.3 Select the Amplifier Gain and Digital Volume Control

In order to select the amplifier gain setting, the designer must determine the maximum power target and the speaker impedance. Once these parameters have been determined, calculate the required output voltage swing which delivers the maximum output power.

Choose the lowest analog gain setting that produces an output voltage swing greater than the required output swing for maximum power. The analog gain can be set by writing to the ANALOG_GAIN bits (bits 3-2, reg 0x06). The default gain setting is 20.7 dBV referenced to 0dBFS input.

8.2.2.4 Select Input Capacitance

Select the bulk capacitors at the PVDD inputs for proper voltage margin and adequate capacitance to support the power requirements. The TAS5722L has very good PVDD PSRR, so the capacitor is more about limiting the ripple and droop for the rest of system than preserving good audio performance. The amount of bulk decoupling can be reduced as long as the droop and ripple is acceptable. One capacitor should be placed near the PVDD inputs at each side of the device. PVDD capacitors should be a low ESR type because they are being used in a high-speed switching application.

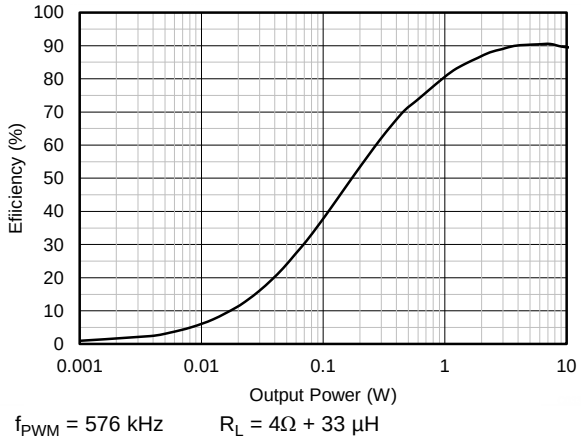
8.2.2.5 Select Decoupling Capacitors

Good quality decoupling capacitors must be added at each of the PVDD inputs to provide good reliability, good audio performance, and to meet regulatory requirements. X5R or better ratings should be used in this application. Consider temperature, ripple current, and voltage overshoots when selecting decoupling capacitors. Also, these decoupling capacitors should be located near the PVDD and GND connections to the device in order to minimize series inductances.

8.2.2.6 Select Bootstrap Capacitors

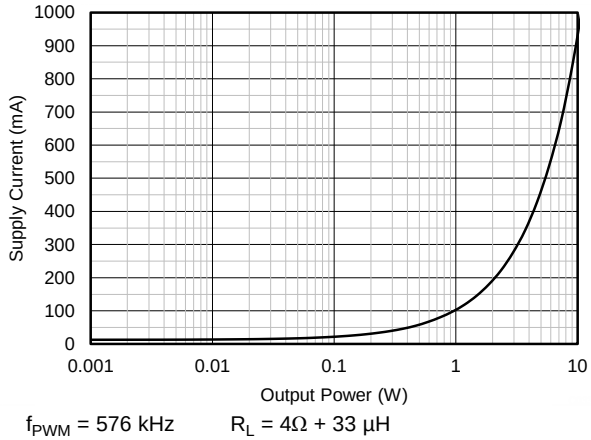
Each of the outputs require bootstrap capacitors to provide gate drive for the high-side output FETs. For this design, use 0.22-µF, 25-V capacitors of X5R quality or better.

8.2.3 Application Performance Plots



f_{PWM} = 576 kHz R_L = 4Ω + 33 µH

图 52. Efficiency vs. Output Power



f_{PWM} = 576 kHz R_L = 4Ω + 33 µH

图 53. Supply Current vs. Output Power

版权 © 2016, Texas Instruments Incorporated

9 Power Supply Recommendations

The power supply requirements for the TAS5722L device consist of one 1.8-V supply to power the low-voltage analog and digital circuitry and one higher-voltage supply to power the output stage of the speaker amplifier. Several on-chip regulators are included on the TAS5722L device to generate the voltages necessary for the internal circuitry of the audio path. It is important to note that the voltage regulators which have been integrated are sized only to provide the current necessary to power the internal circuitry. The external pins are provided only as a connection point for off-chip bypass capacitors to filter the supply. Connecting external circuitry to these regulator outputs may result in reduced performance and damage to the device.

The TAS5722L requires two power supplies. A 1.8-V supply, called DVDD, is required to power the digital section of the device. A higher-voltage supply, between 4.5 V and 17 V, supplies the analog circuitry (AVDD) and the power stage (PVDD). The AVDD supply feeds several LDOs including GVDD, VREG, and VCOM. These LDO outputs are connected to external pins for filtering purposes, but should not be connected to external circuits. These LDO outputs have been sized to provide current necessary for internal functions but not for external loading.

10 Layout

10.1 Layout Guidelines

- Pay special attention to the power stage power supply layout. Each half bridge has two PVDD input pins so that decoupling capacitors can be placed nearby. Use at least a 0.1-µF capacitor of X5R quality or better for each set of inputs.
- Keep the current circulating loops containing the supply decoupling capacitors, the H-bridges in the device and the connections to the speakers as tight as possible to reduce emissions.
- Use ground planes to provide the lowest impedance for power and signal current between the device and the decoupling capacitors. The area directly under the device should be treated as a central ground area for the device, and all device grounds must be connected directly to that area.
- Use a via pattern to connect the area directly under the device to the ground planes in copper layers below the surface. This connection helps to dissipate heat from the device.
- Avoid interrupting the ground plane with circular traces around the device. Interruption disconnects the copper and interrupt flow of heat and current. Radial copper traces are better to use if necessary.

版权 © 2016, Texas Instruments Incorporated

10.2 Layout Example

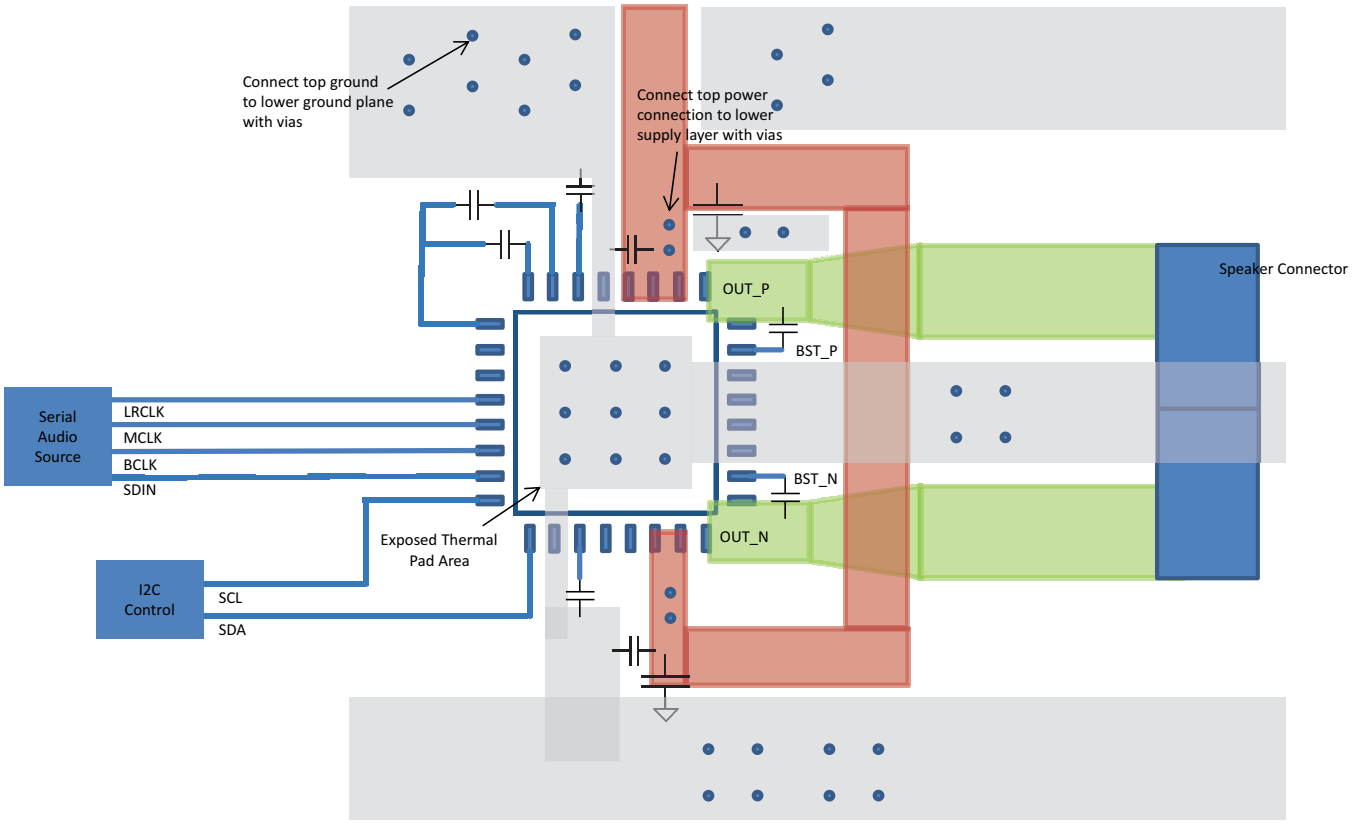


图 54. Layout Example

版权 © 2016, Texas Instruments Incorporated

11 器件和文档支持

11.1 商标

All trademarks are the property of their respective owners.

11.2 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

Copyright © 2016, Texas Instruments Incorporated

12.1 Package Option Addendum

12.1.1 Packaging Information

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4) (5)
TAS5722LRSMR	ACTIVE	VQFN	RSM	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	–25 to 85	TAS 5722L
TAS5722LRSMT	ACTIVE	VQFN	RSM	32	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	–25 to 85	TAS 5722L

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PRE_PROD Unannounced device, not in production, not available for mass market, nor on the web, samples not available.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device

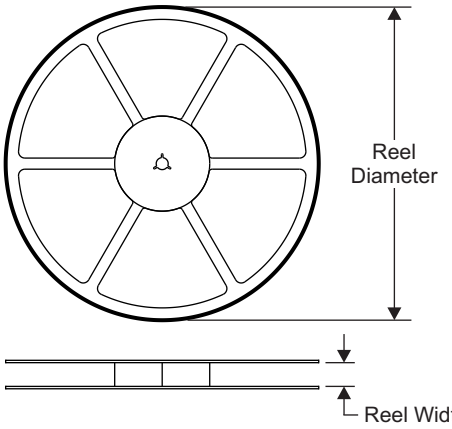
(5) Multiple Device markings will be inside parentheses. Only on Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

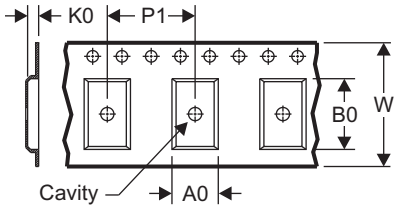
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

12.1.2 Tape and Reel Information

REEL DIMENSIONS

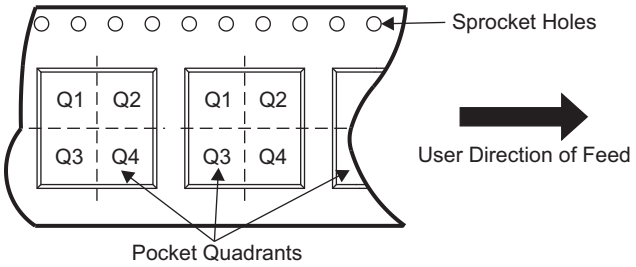


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

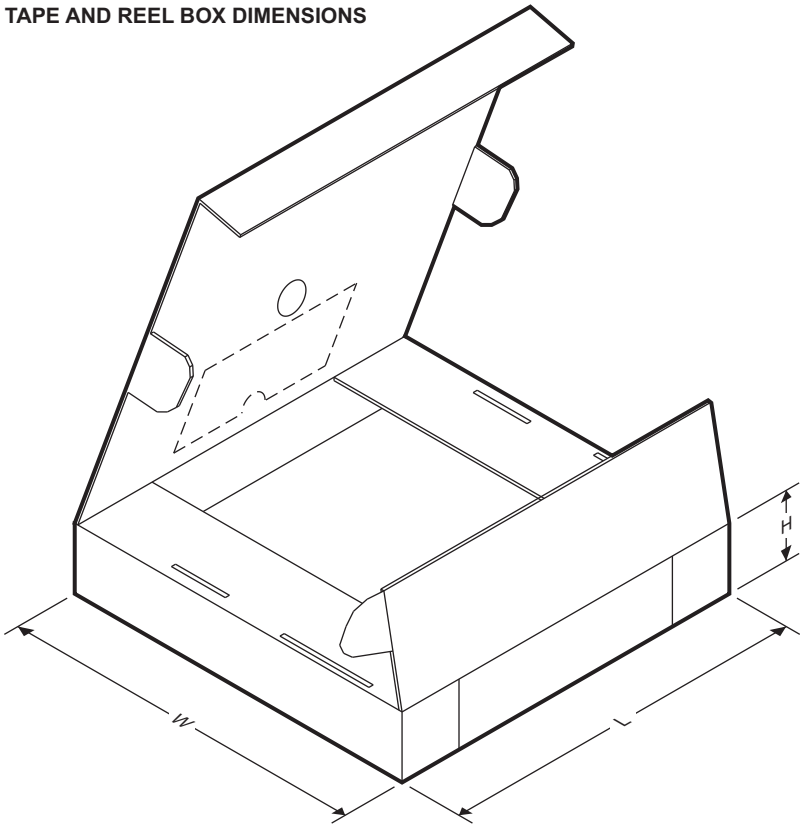
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TAS5722LRSMR	VQFN	RSM	32	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TAS5722LRSMT	VQFN	RSM	32	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

Copyright © 2016, Texas Instruments Incorporated

TAPE AND REEL BOX DIMENSIONS



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TAS5722LRSMR	VQFN	RSM	32	3000	367.0	367.0	35.0
TAS5722LRSMT	VQFN	RSM	32	250	210.0	185.0	35.0

版权 © 2016, Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TAS5722LRSMR	ACTIVE	VQFN	RSM	32	3000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-25 to 85	TAS 5722L	Samples
TAS5722LRSMT	ACTIVE	VQFN	RSM	32	250	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-25 to 85	TAS 5722L	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

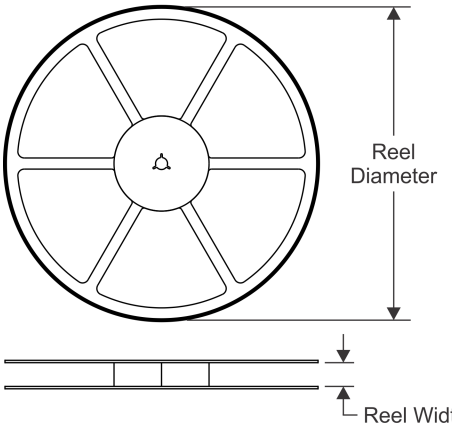
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

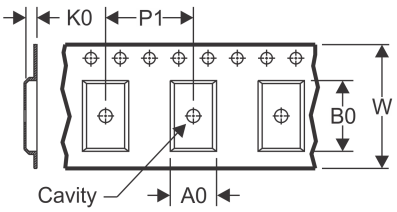
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

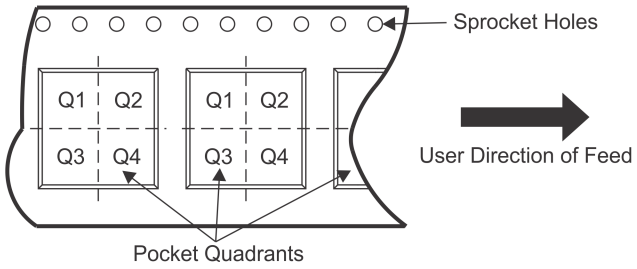


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

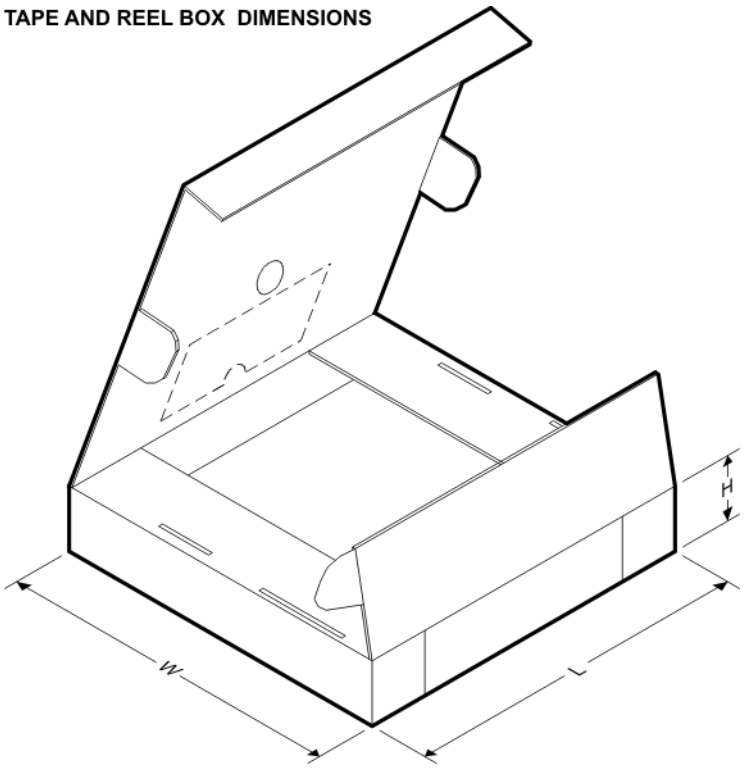
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TAS5722LRSMR	VQFN	RSM	32	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TAS5722LRSMT	VQFN	RSM	32	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TAS5722LRSMR	VQFN	RSM	32	3000	367.0	367.0	35.0
TAS5722LRSMT	VQFN	RSM	32	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

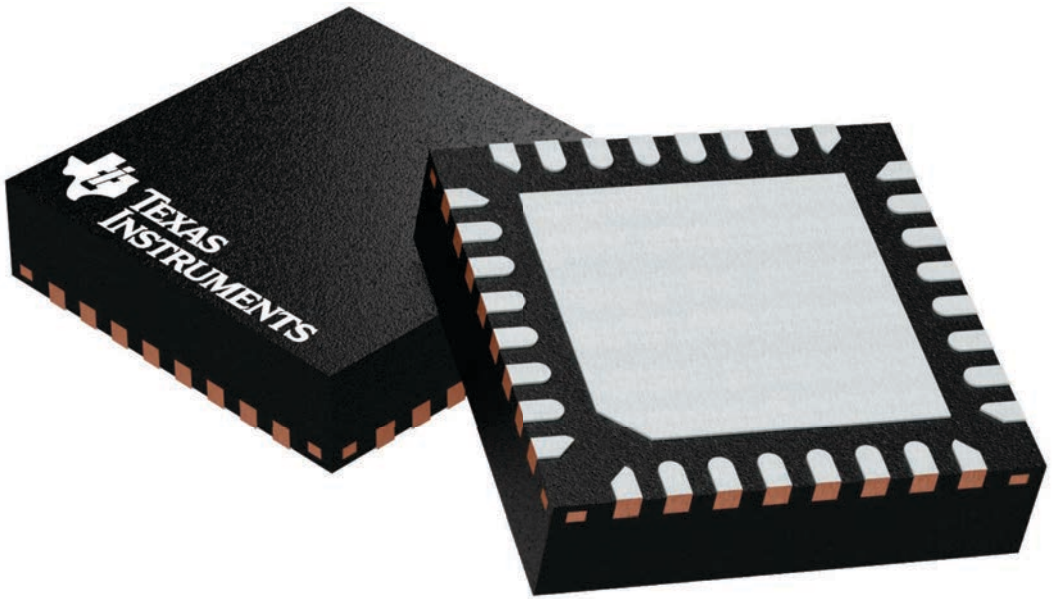
RSM 32

VQFN - 1 mm max height

4 x 4, 0.4 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224982/A

重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2022，德州仪器 (TI) 公司